



16th SPIE Int'l Symposium on Smart Structures and Materials

Nano-Bio Quantum Technology for Device Specific Materials

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Areas to be discussed

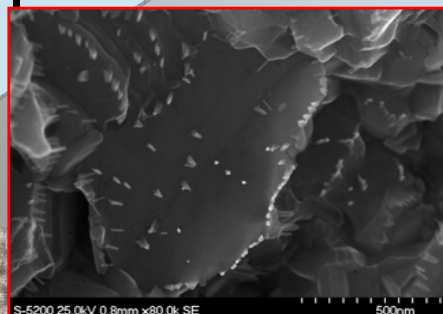
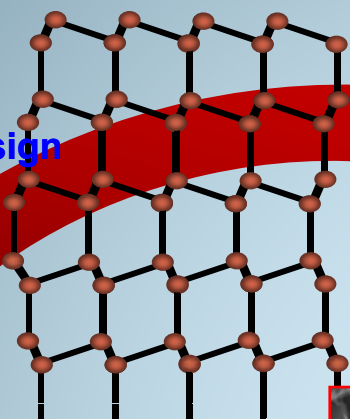
- Thermoelectric Materials
- Smart Optical Materials
 - Quantum Apertures
 - Micro Spectrometers
 - Light Control Ferroelectric Materials
- Ferritin Molecules
 - Biotemplates for Nanopartices
 - Bionanobattery



ADVANCED THERMOELECTRIC MATERIAL DEVELOPMENT

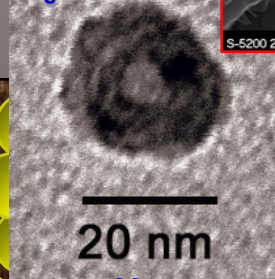
Twin Crystal with Stacking Defect:
Better Material Design
than Superlattice

SiGe



Material Prepared

STEM Image of Au Voigen



Home-grown Voigen

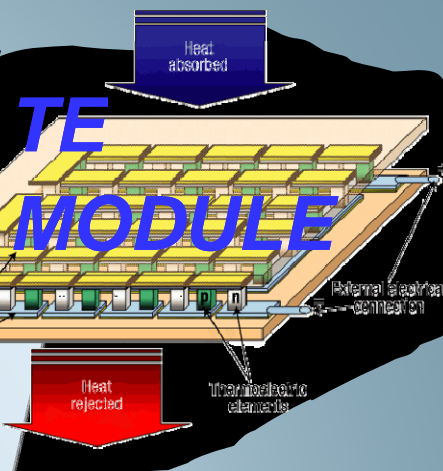
High Performance Semiconductor



Si_{1-y}Ge_y Lattice-matched condition

Produced @ NASA LaRC

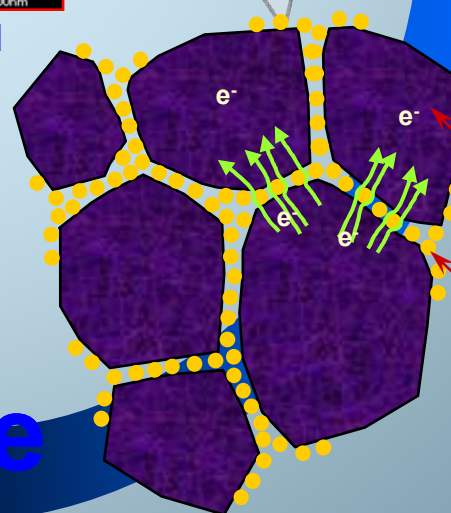
Initial Concept



TE MODULE

Hot Press / Low Pressure Material Process

BiTe



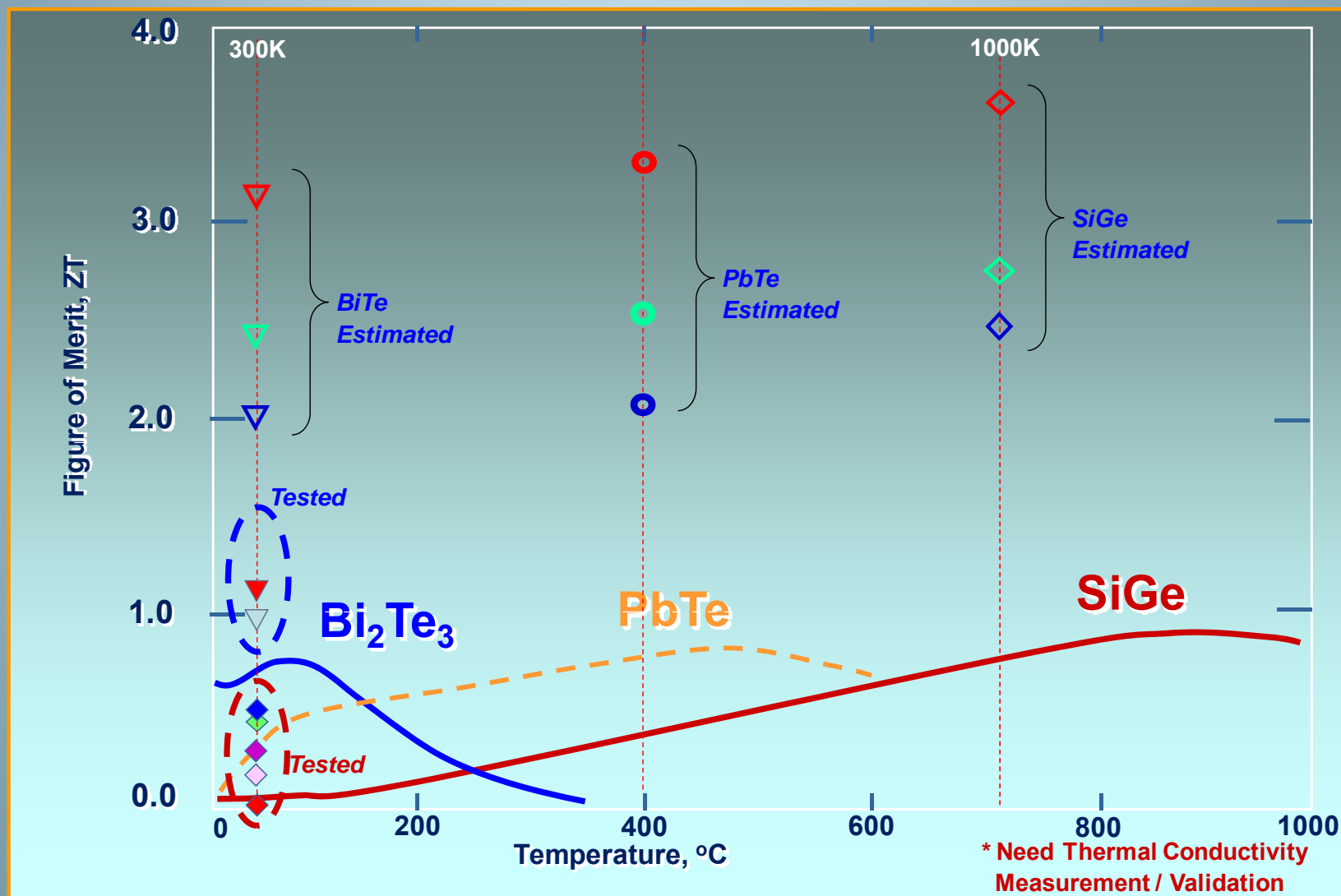
Bi₂Te₃ Nanocrystals
40 – 60 nm

Metallic Nanoshell:
2 – 20 nm

Electrical conductor
Phonon scatterer

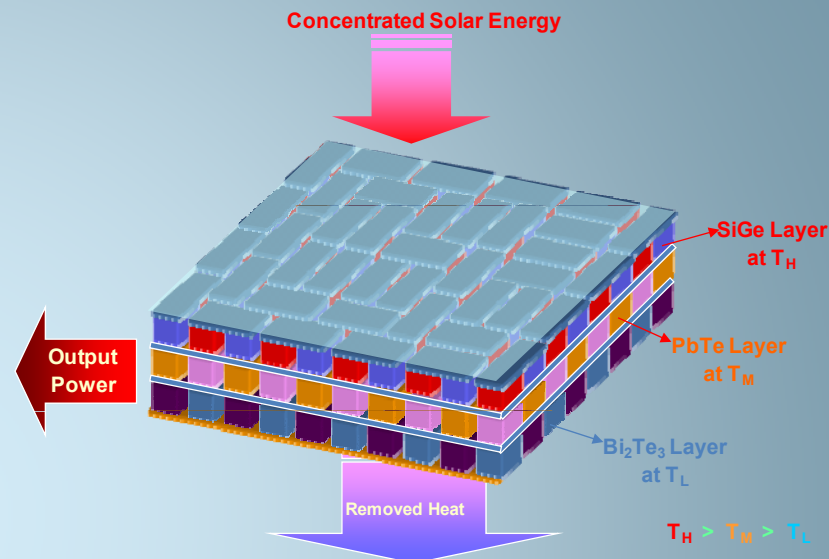
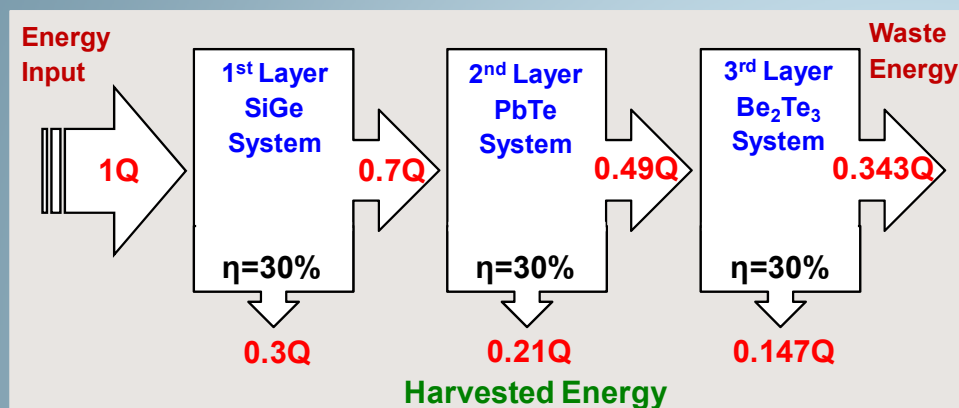


TE Performance Summary: Results & Projections





ATE Device for Solar Energy Conversion

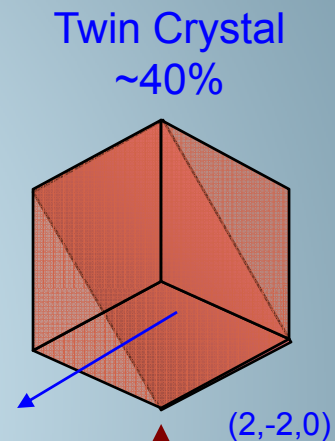
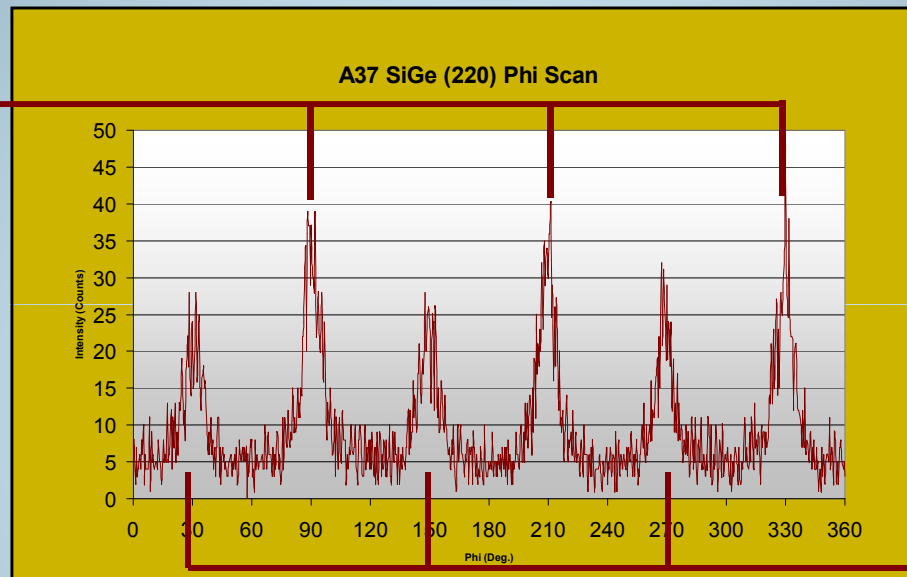
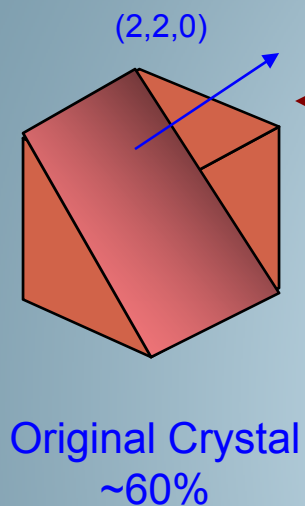


TE Tandem System	TE FoM ≥ 1.5 $\eta = 10\%$		TE FoM ≥ 3.5 $\eta = 20\%$		TE FoM ≥ 4.5 $\eta = 30\%$		Solar Cells
	Loaded Energy, Q	η	Loaded Energy, Q	η	Loaded Energy, Q	η	η
1st Layer (Hi T)	1Q in 0.9Q out	10 %	1Q in 0.8Q out	20 %	1Q in 0.7Q out	30 %	30 % (?) for membrane PV
2nd Layer (Med T)	0.9 in 0.81Q out	10 %	0.8 in 0.64Q out	20 %	0.7 in 0.49Q out	30 %	
3rd Layer (Low T)	0.81Q in 0.729Q out	10 %	0.64Q in 0.512Q out	20 %	0.49Q in 0.343Q out	30 %	
Cascade Efficiency	0.271Q Harvested	27 %	0.488Q Harvested	48 %	0.657Q Harvested	65 %	

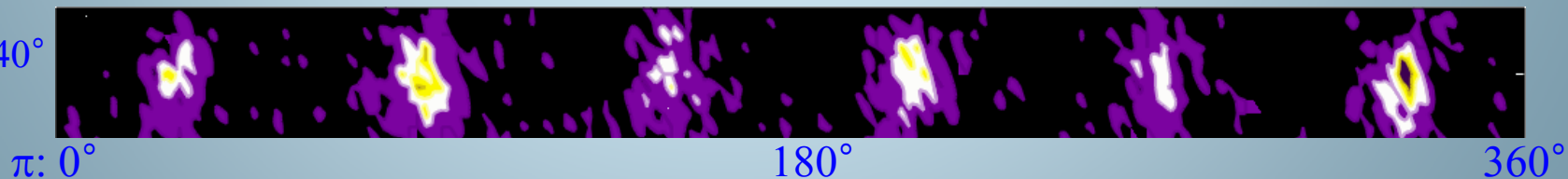


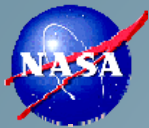
Si-Ge: Twin-Lattice Structure

Symmetry Breaking to 60:40



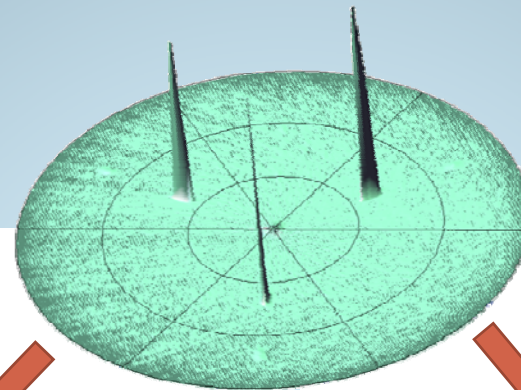
$\Psi: 32 \sim 40^\circ$



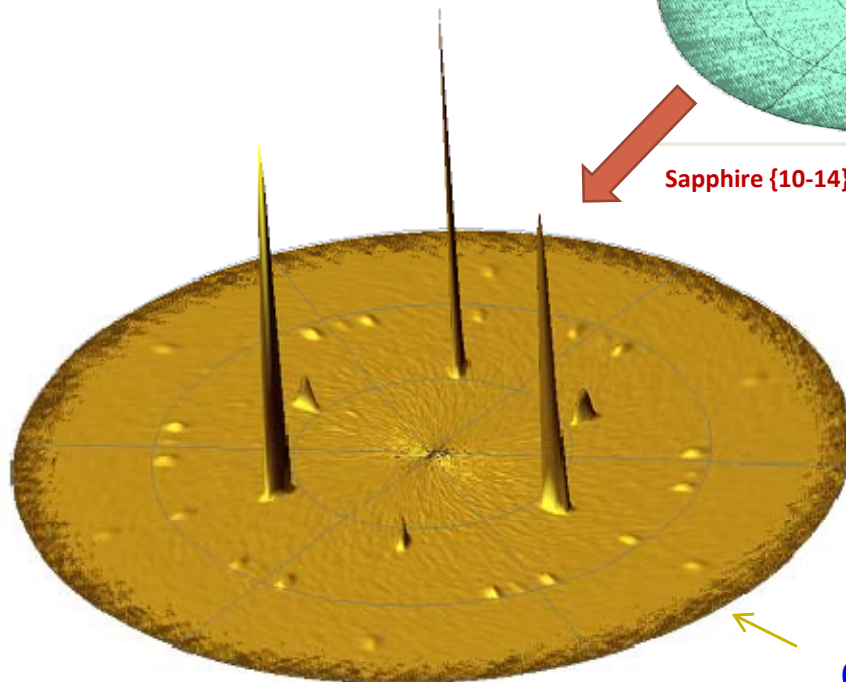


Rhombohedral Hybrid Band-Gap Engineering

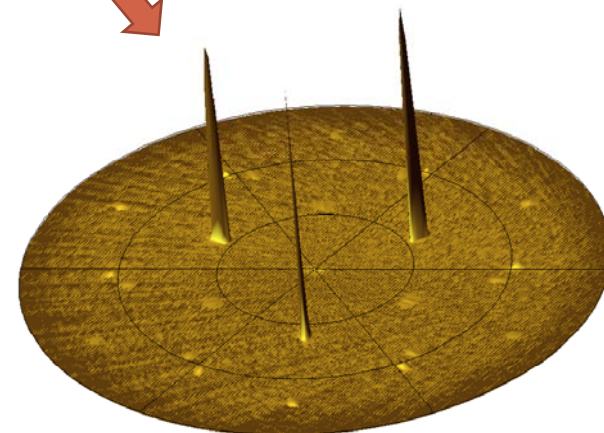
Two Single Crystalline Alignments



Sapphire {10-14}



SiGe {220}, Low Temperature



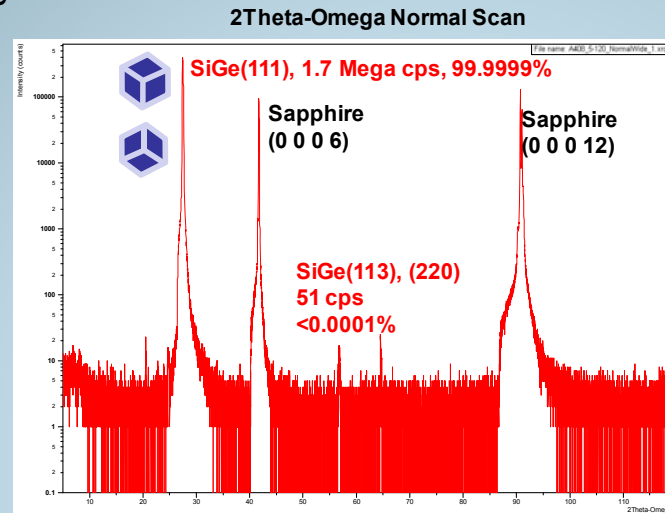
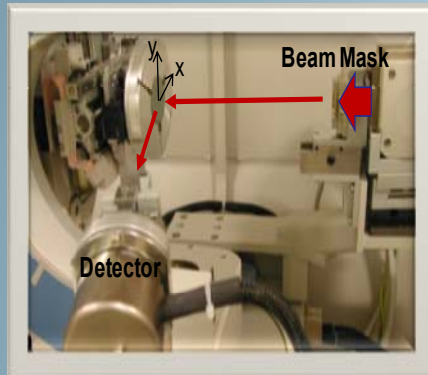
SiGe {220}, High Temperature

60 degree
difference



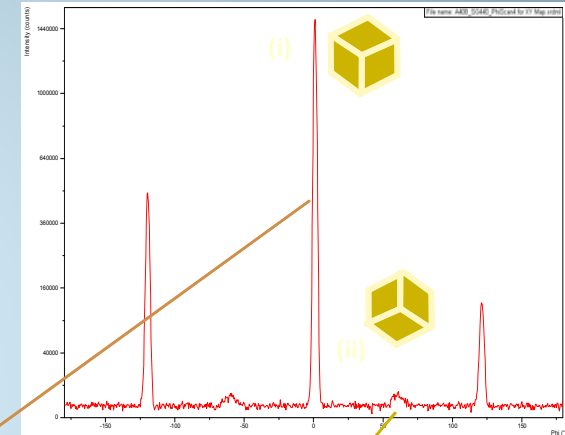
Wafer Mapping 1. (99.9999% single crystal)

Asymmetric angles for XY mapping
with Point X-ray source

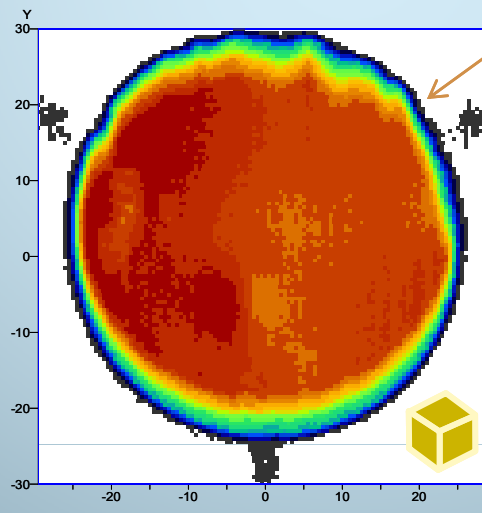
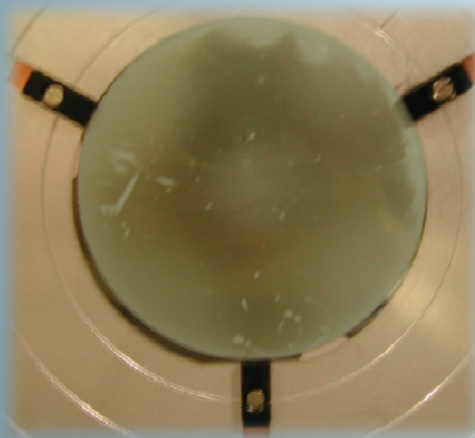


Point X-ray source for mapping

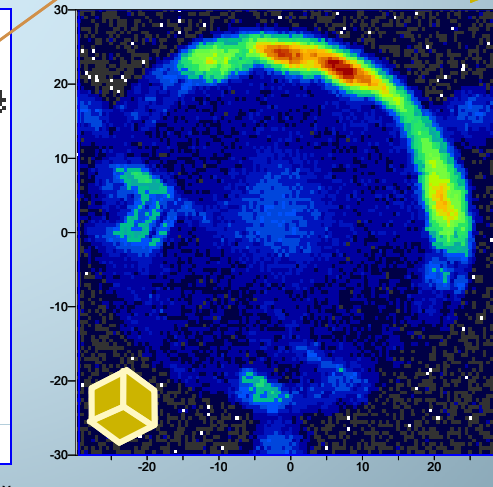
SiGe(440) Untilted Asymmetric Phi-Scan



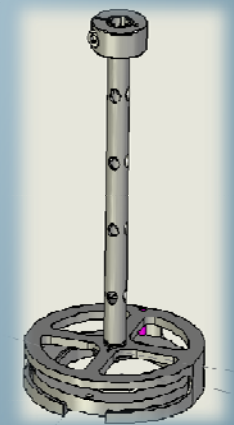
Wafer Mapping



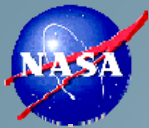
(i) Majority single crystal map



(ii) Defect map: Primary twin crystal rotated by 60° on (111) plane



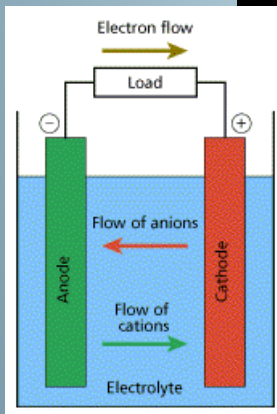
Sample cage created + shaped thermal shadow



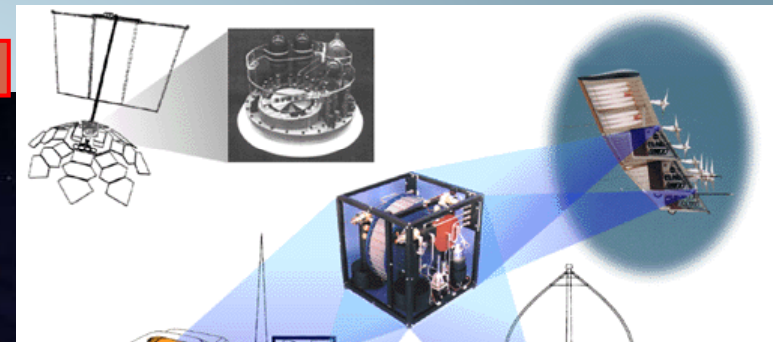
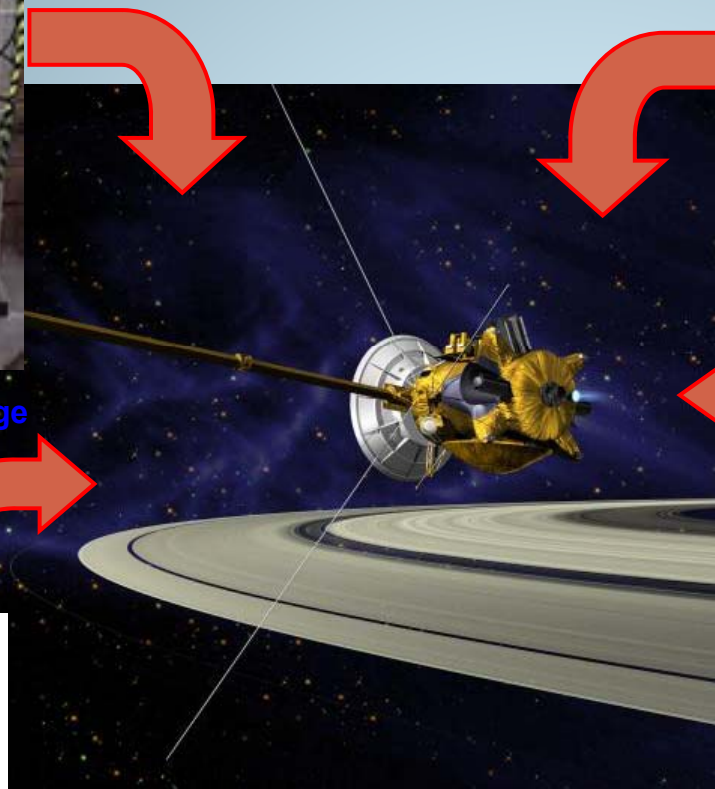
Power Sources for Spacecrafts



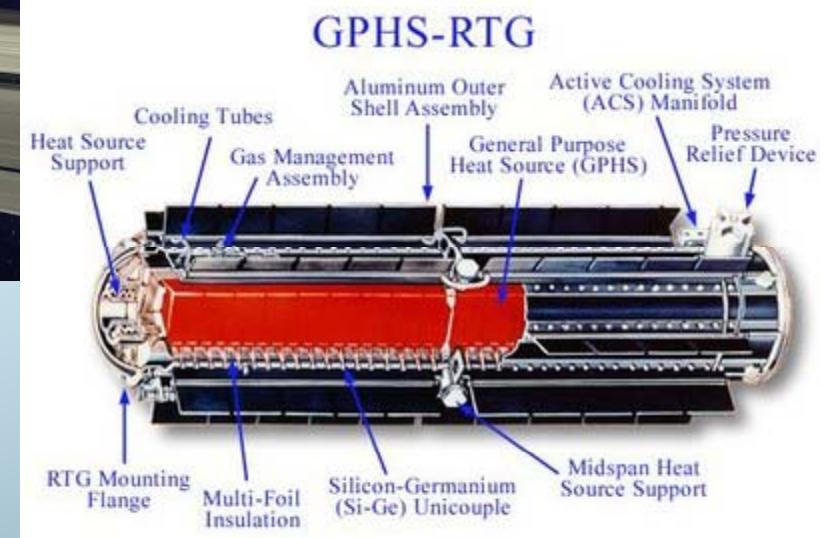
Fly-wheel Power Storage



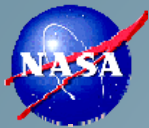
Canister-based Battery



Fuel Cells



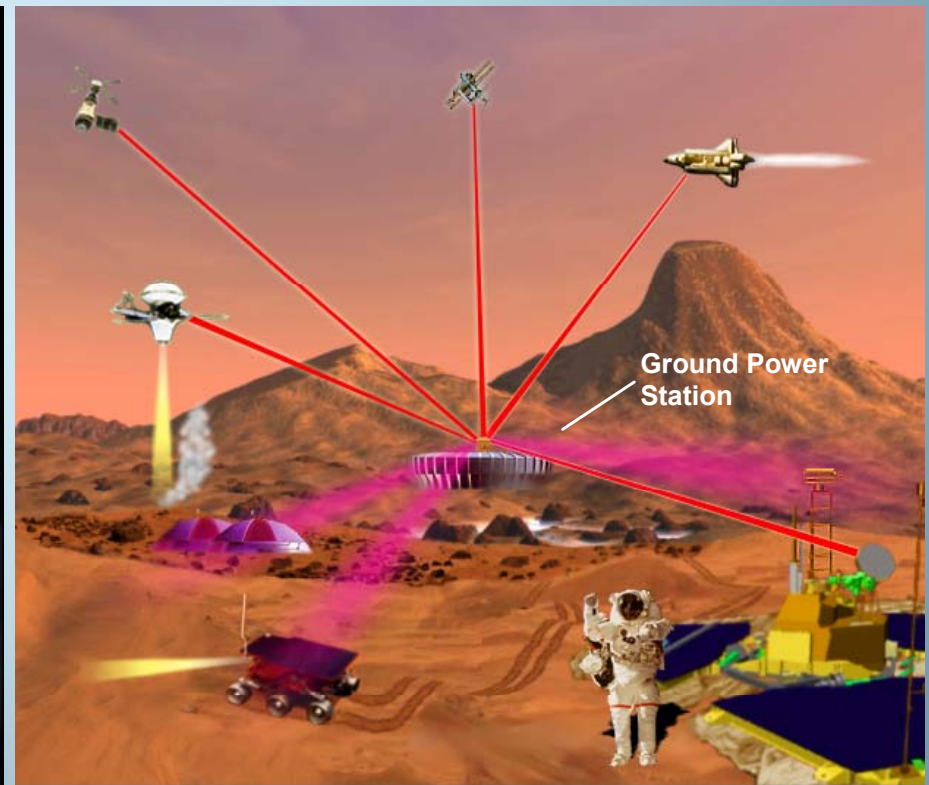
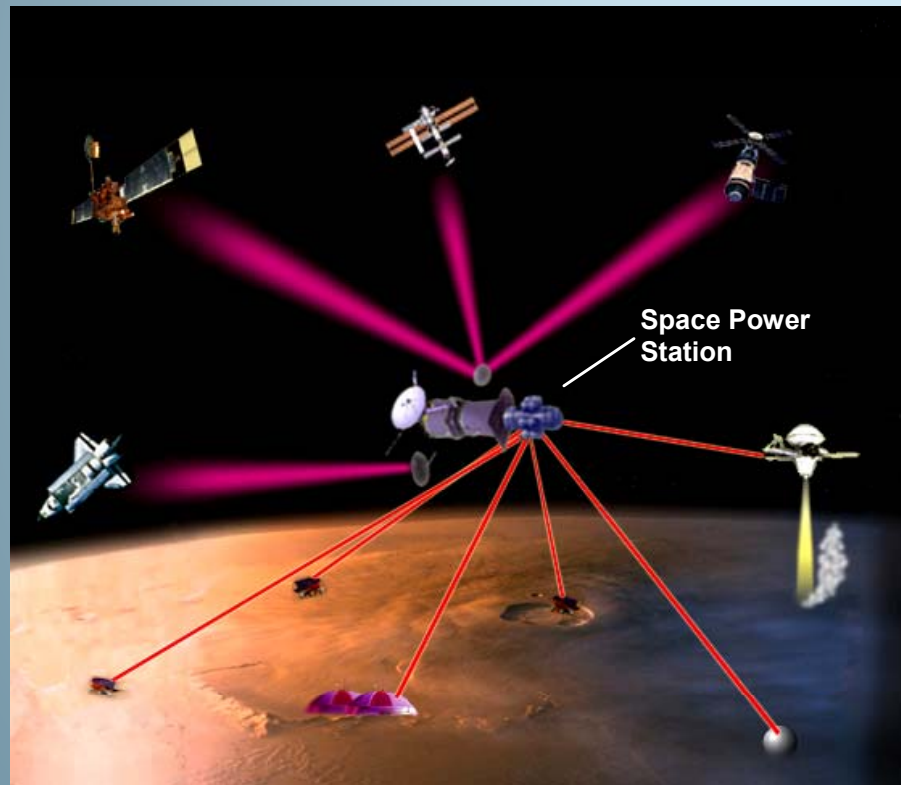
Radioisotope Thermoelectric Generators (RTG)



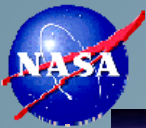
Advanced Thermoelectric Power Generation and Transmission System

The proposed system encompasses three subsystems:

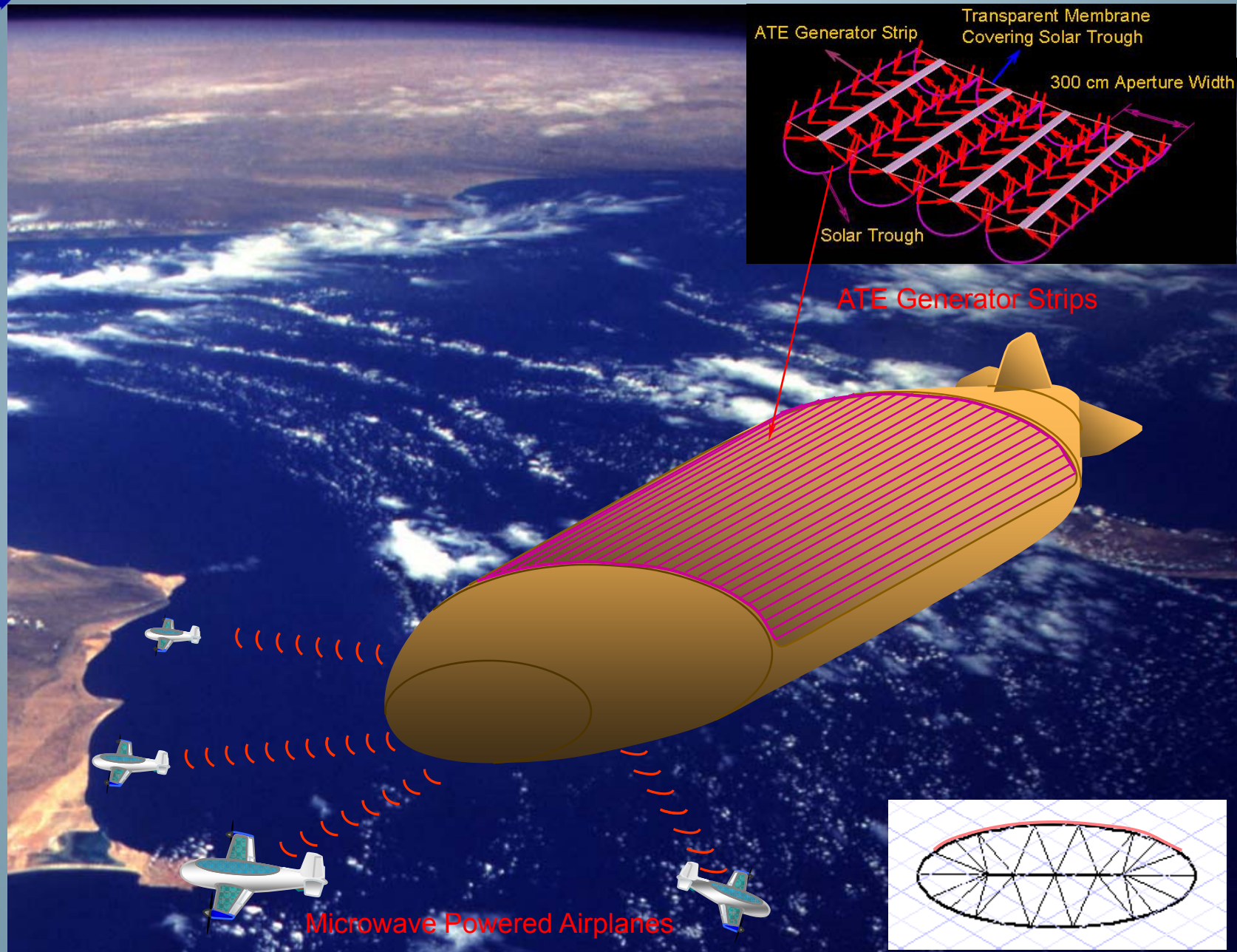
1. Radioisotope Power (RIP) subsystem
2. Advanced Thermoelectric Generator (ATEG) subsystem
3. Wireless Power Transmission (WPT) subsystem

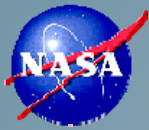


Artist's concepts of Mars space power station installed with WPT-ATEG system: space system (left) and ground system (right).



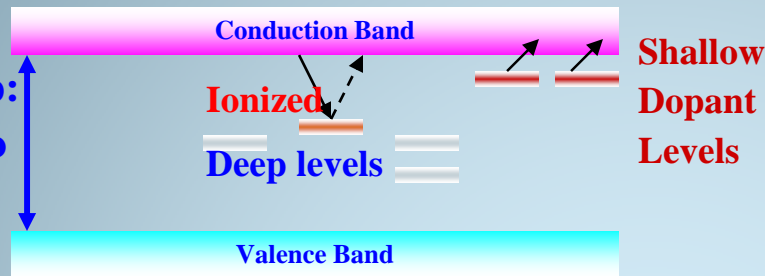
Solar Thermoelectrics: HAA Model with Ellipsoidal Cross-Section



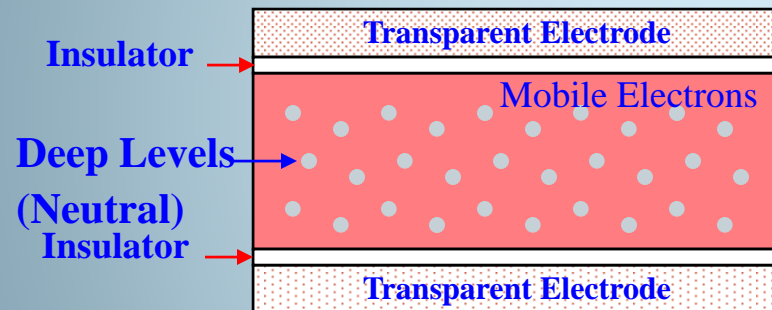


Distribution of Carriers and Ionization of Deep Levels

Wide Bandgap:
Transparent to
visible lights



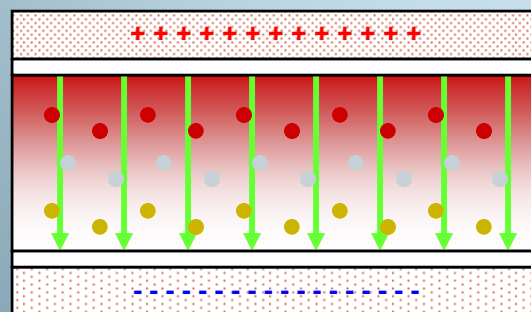
(1) Without Electric Field



(2) With Electric Field: Redistribution of Mobile Electrons

Negatively
charged
deep levels

Positively charged
deep levels



For wide band-gap materials:

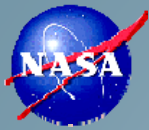
- Transparent to visible lights
- Carriers in **shallow dopant levels** are mobile to conduction or valence band.
- Deep levels in crystal imperfection capture or emit mobile charges.
- Bandgap structure is ionized with the loss or capture of carriers.

For $|\vec{E}| = 0$,

- Mobile electrons distributed **uniformly** in media layer.
- Most of the deep levels are **neutral** in this state.

For $|\vec{E}| \gg 0$,

- Mobile carriers (electrons in the picture) are **re-distributed**
- Deep levels are **ionized** and form **new color centers**.
- Absorption coefficient and index of refraction are changed



Hall Effect Measurement

As Grown ScN on Al_2O_3

● RESULTS	B = 0.51 [T]	D = 0.28 [um]
Carrier Density: $\times 10^4$		
Nb = -5.7963E+20 [/cm ³]	Ns = -1.6230E+16 [/cm ²]	
μ = 11.50203 [cm ² /V·s]	Rh = -1.0769E-02 [m ² /C]	Conductivity: $\times 10^5$
ρ = 9.3631E-04 [Ω ·cm]	σ = 1.0680E+03 [1/ Ω ·cm]	
delta_R = 1.9616E-02 [Ω]	alpha = 0.12167	
Nb : Bulk concentration μ : Mobility ρ : Bulk resistivity delta_R : magnetoresistance		
Ns : Sheet concentration Rh : Hall coefficient σ : Conductivity alpha : V/H Ratio of Resistance		

Intrinsic GaN on Al_2O_3

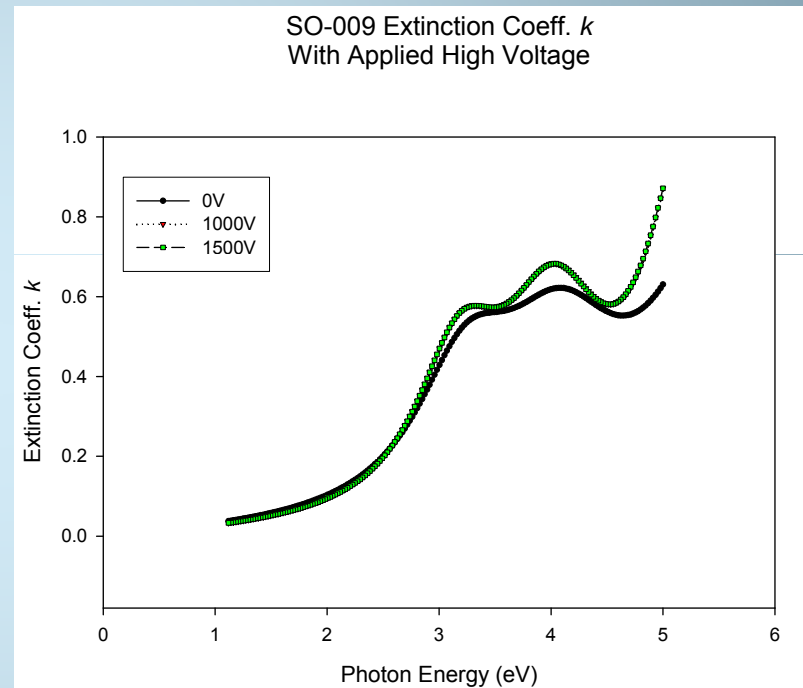
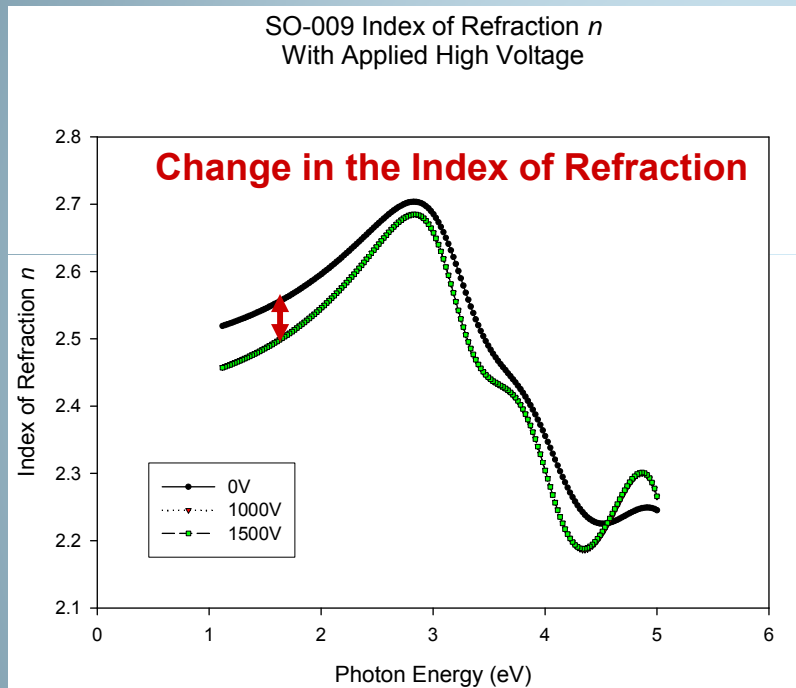
● RESULTS	B = 0.51 [T]	D = 0.397 [um]
Nb = -6.6835E+16 [/cm ³]	Ns = -2.6534E+12 [/cm ²]	
μ = 2.22096 [cm ² /V·s]	Rh = -93.39652 [m ² /C]	
ρ = 52.87408 [Ω ·cm]	σ = 1.8913E-02 [1/ Ω ·cm]	
delta_R = 1.5208E+04 [Ω]	alpha = 0.16824	
Nb : Bulk concentration μ : Mobility ρ : Bulk resistivity delta_R : magnetoresistance		
Ns : Sheet concentration Rh : Hall coefficient σ : Conductivity alpha : V/H Ratio of Resistance		



ScN grown on c-axis Sapphire (Al_2O_3) shows 10,000 times higher electron concentration than intrinsic GaN. This unintentional high-background- doping gives mobile charges in the media. With the applied electric field, the redistribution of mobile charges changes the index of refraction.



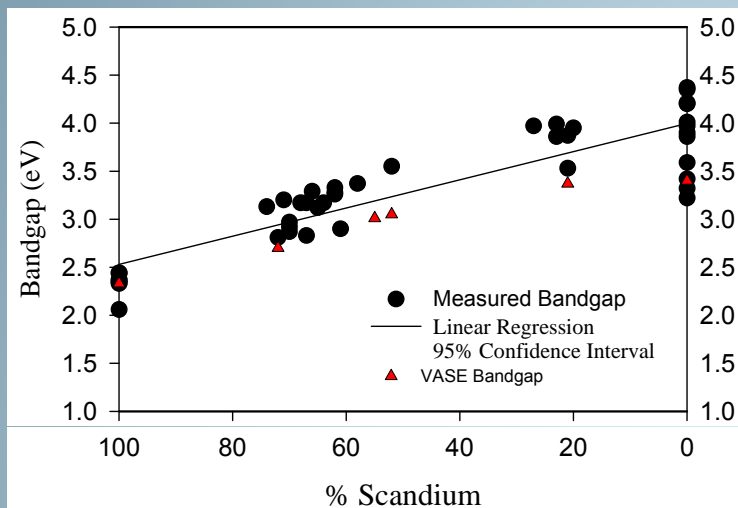
Change of the Index of Refraction in ScN



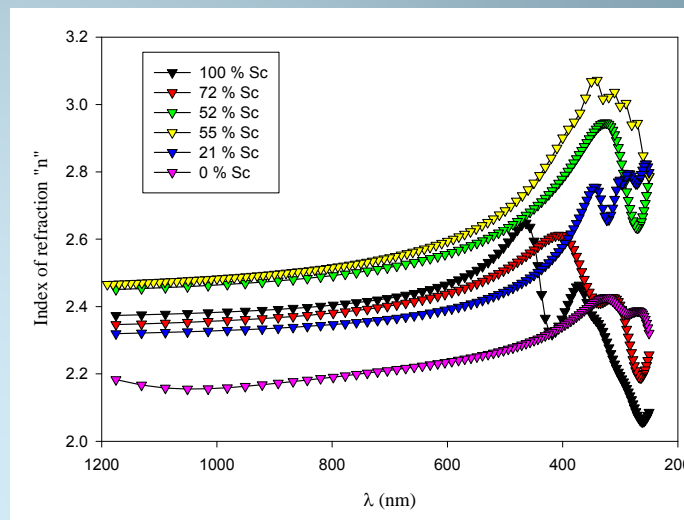
ScN film shows the change in the index of refraction with the applied electric field. The electric field was applied with a few mm gap. The required voltage can be reduced in the optimized structure.



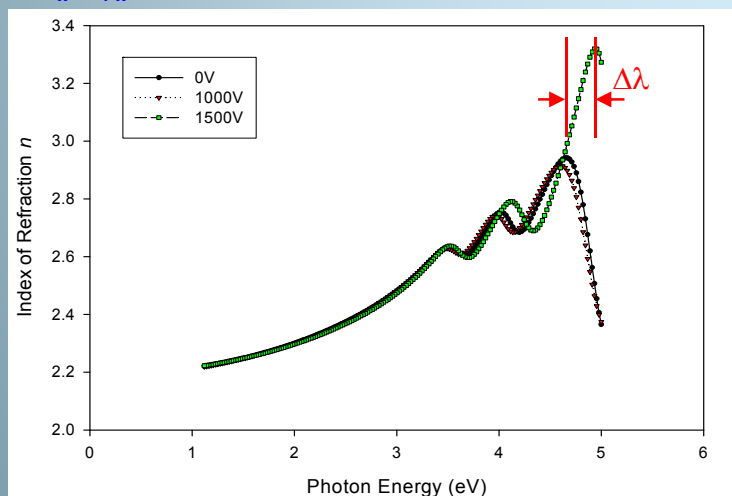
$Ga_xSc_{1-x}N$ Alloy System



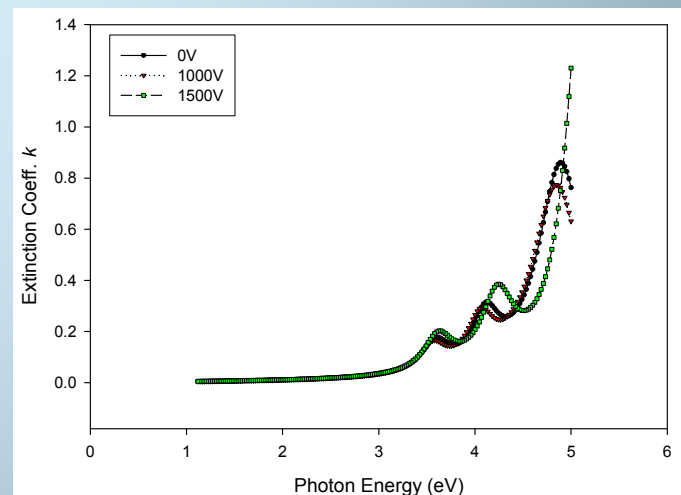
Bandgap Energy versus Scandium Concentration in $Ga_xSc_{1-x}N$ alloy system.



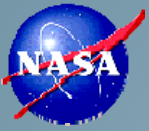
Index of refraction in the region below optical absorption



A thin-film of scandium-alloyed gallium nitride ($Ga_xSc_{1-x}N$, $x=0.47$) developed on a quartz substrate shows both the spectral and refractive index shifts very clearly from 3.5 eV to higher photon energy.



Extinction coefficient data shows a similar response as refractive index in the left, very clearly from 3.5 eV to higher photon energy.

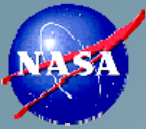


Adaptive Optical Components

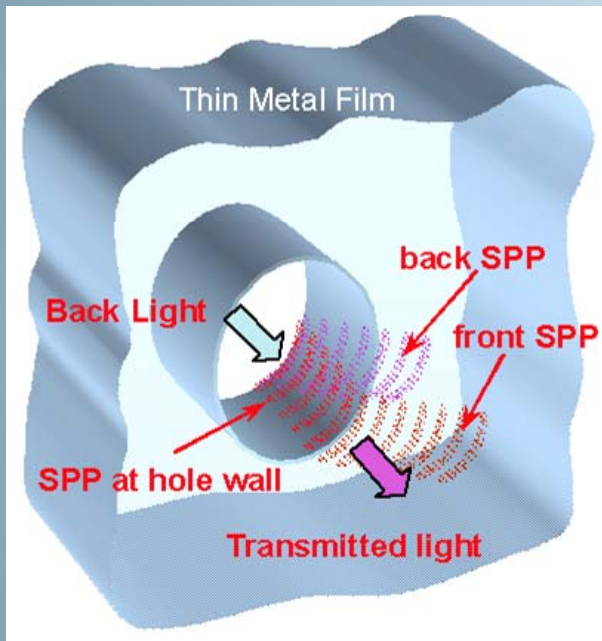


Geometric grating effect from the reflective array, fabricated at NASA LaRC

- The goal of Adaptive Optical Components: Adding a **programmability** to the conventional optical components, including lens, grating, apertures, filters and reflectors. The same optical component can be programmed for different wavelengths and polarizations.
- It can reduce the total weight of satellites and increase the working range and sensitivity of device with **versatility**.

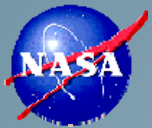


Plasmon Enhanced Transmission

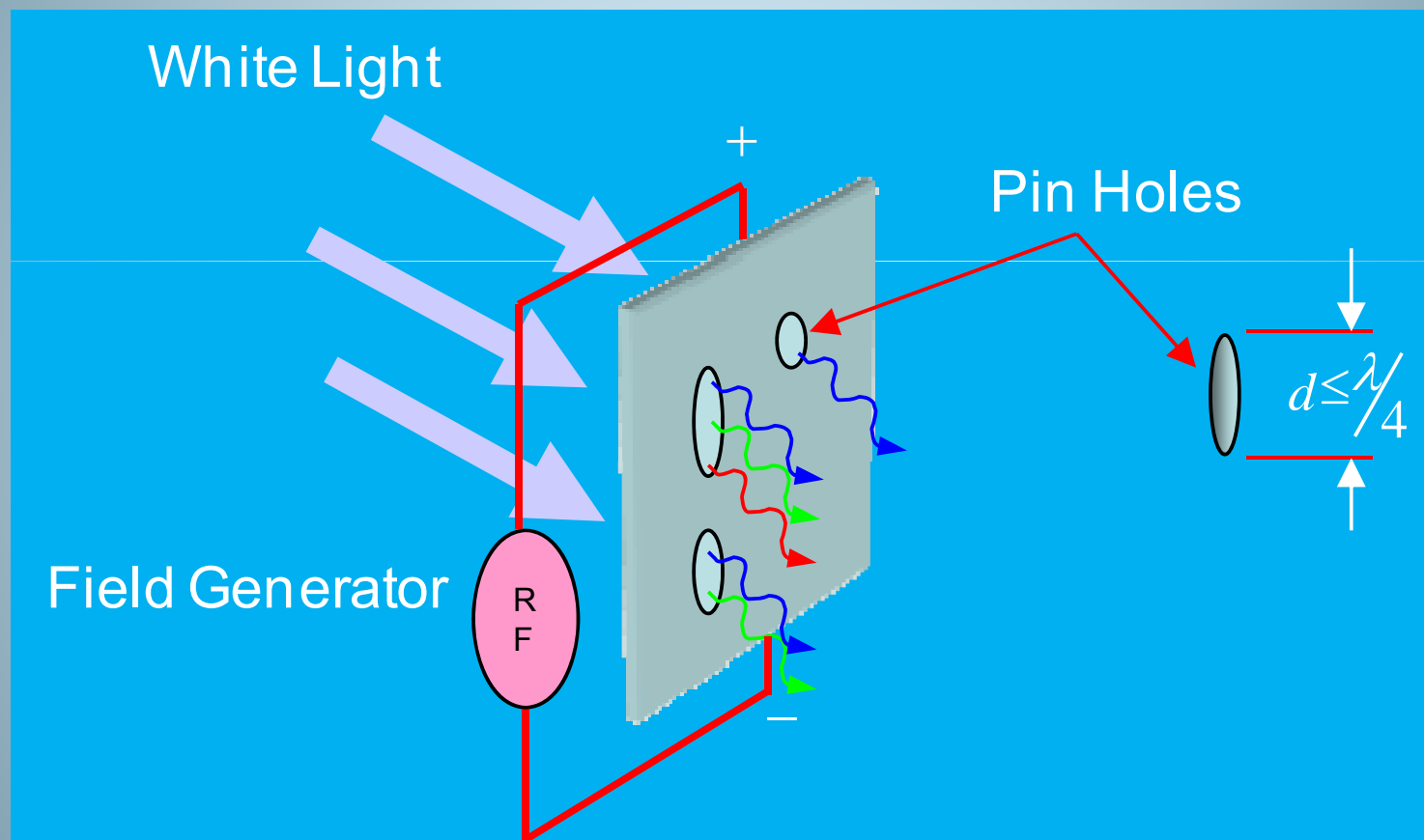


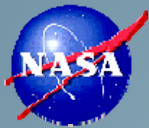
Transmission through
a quantum aperture

- Metal surface has the collective movement of the electrons at the surface; it is called the surface plasmon, propagating on the surface only.
- The **skin-depth** of a good conductive metal is very shallow; a hundred nanometer metal film is enough to block the light penetration.
- The transmission of the photons through a hole smaller than $1/4$ is controlled by the **surface plasmons** in the hole.
- The incident light generates the back surface plasmon. Surface plasmon **propagates through the surface** of the hole. On the front side, the surface plasmon radiates the light again.
- Other experiments indicate there is no enhanced transmission of a long wavelength light through tiny holes in Ge, where there is no plasmon. Only a good conductor surface has plasmon.

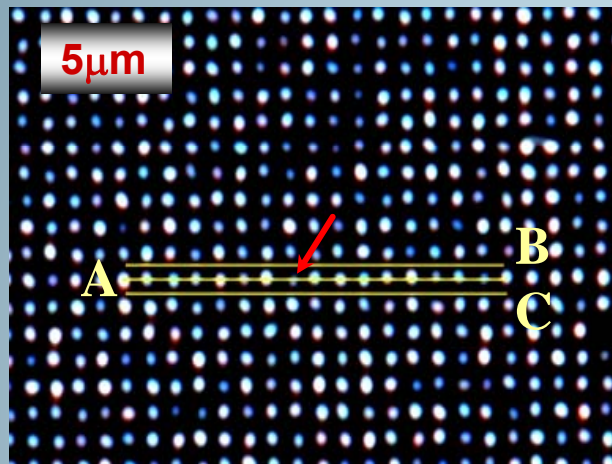


Nano Apertures

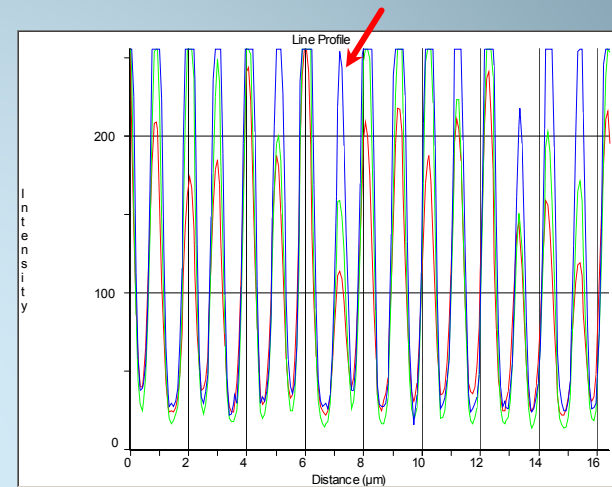




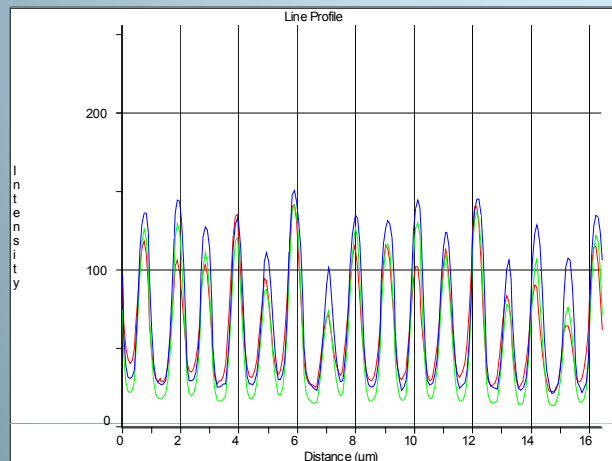
Microscopic Spectral Distribution From Individual Quantum Aperture with 200nm Diameter



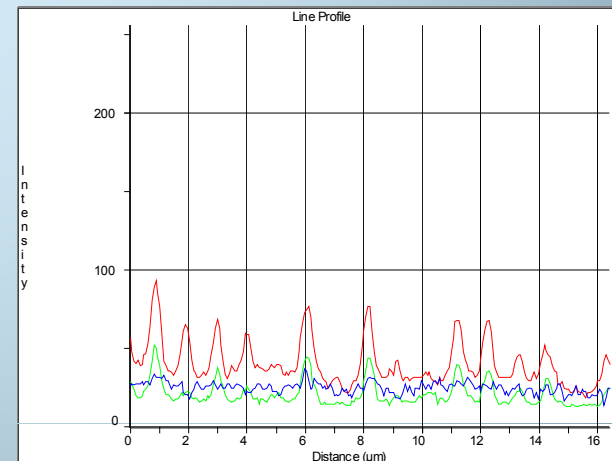
Transmitted Light



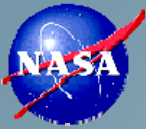
Center Line A: Strong Blue



Sum of Area between B and C:
Close to White Light with Blue



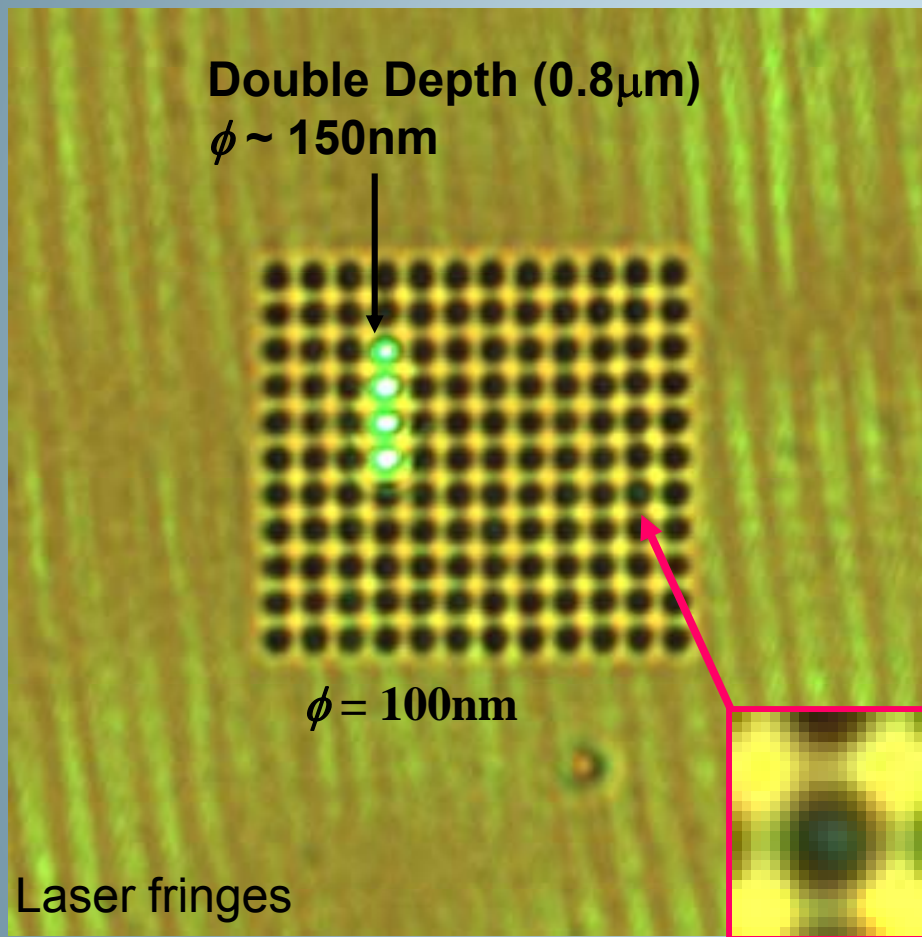
Boundary Line B or C:
Dark Red



Selected Light Transmission

Laser (532nm) + Front side illumination

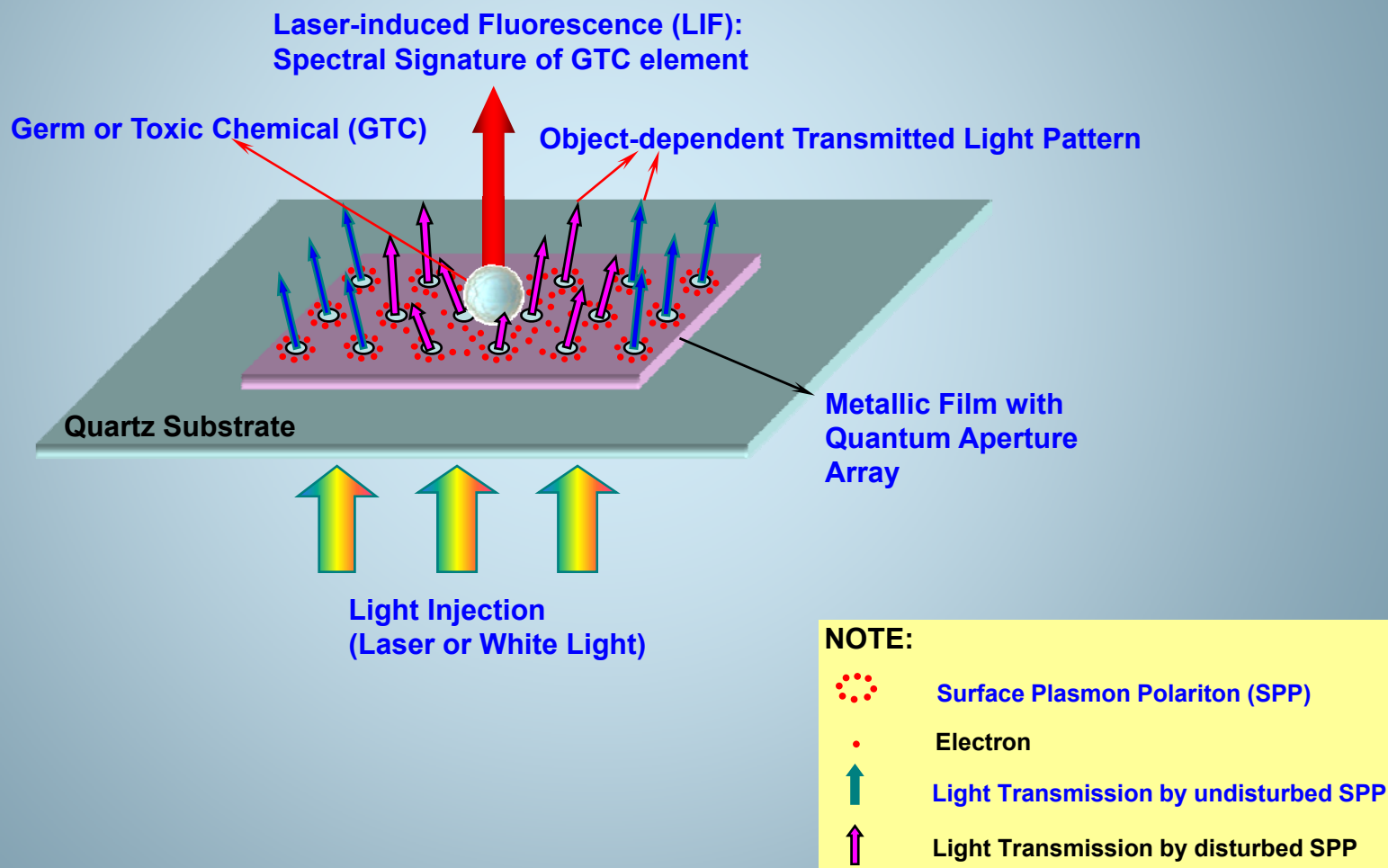
Laser (630nm) backside illumination only

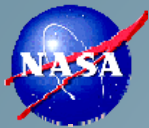


Green light passes through.



Dual Sensing Capable Germ or Toxic Chemical (GTC) Sensor using Quantum Aperture Array with Surface Plasmon Polariton (SPP)





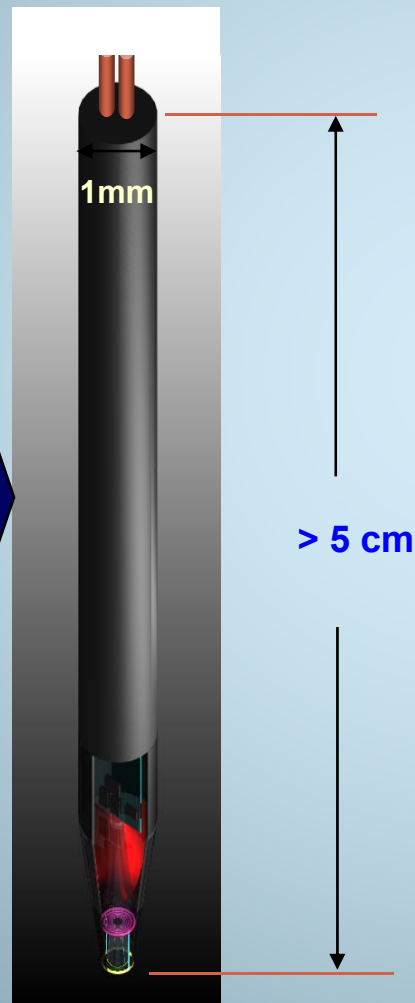
Micro Spectrometer (μ -SM) Applications

Medical Application for Neurosensing

For Space Exploration

Medical Sensors:

- Tiny form factor < 1 mm
- Flexible pin
- Sensor fusion capable
- Power & telemetry
- Redundancy feature



Leveraging Factors

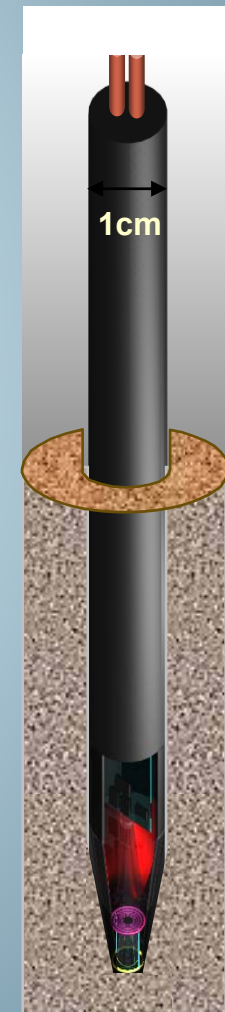
Space:

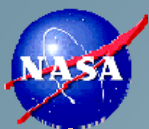
- μ -SM imbedded rover tires
- μ -SM imbedded Astronaut's shoes
- μ -SM imbedded canes or darts
- Hyperspectral imaging

Aeronautics:

- Engine combustion monitoring
- Fuel leak detection
- Hyperspectral Lidar imaging

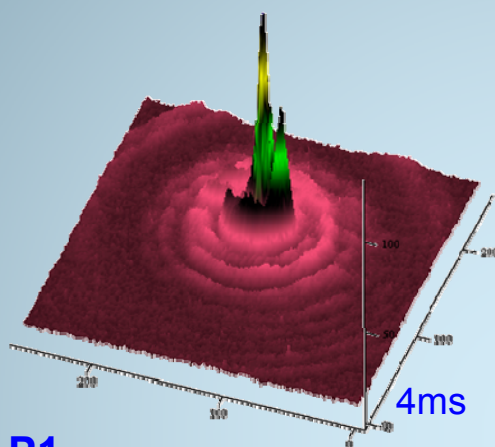
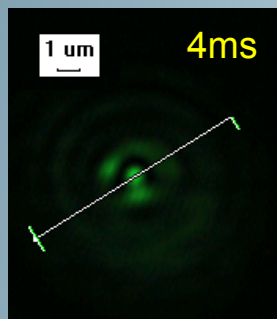
Can be used in
Tumble-weed type
planetary surface explorer



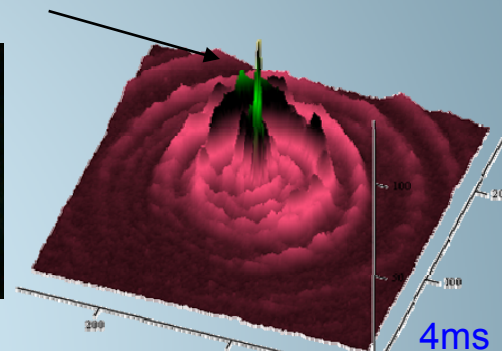
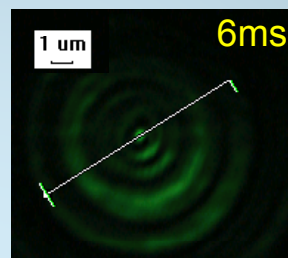


Sharpness of focal point P1 and PX with a green laser ($\lambda=532\text{nm}$)

10 mW Laser in 2mm diameter (0.3 W/cm^2) can
have a focused power density = 10^5 Watt/cm^2

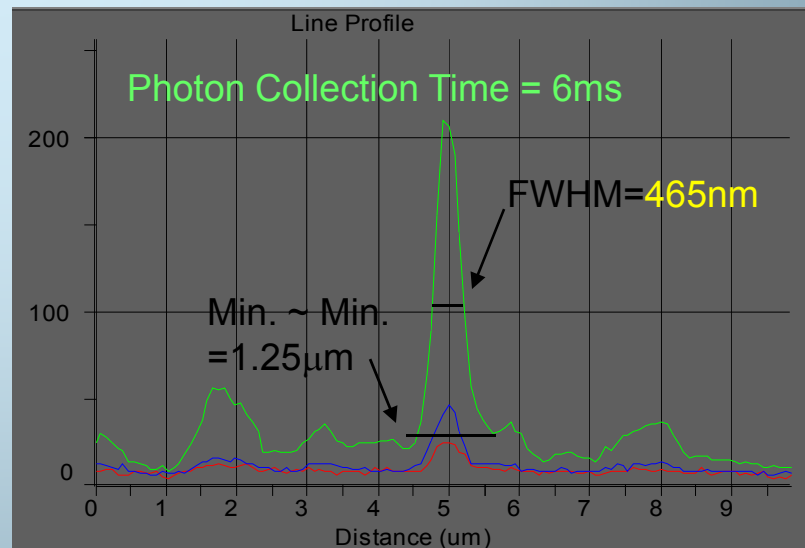
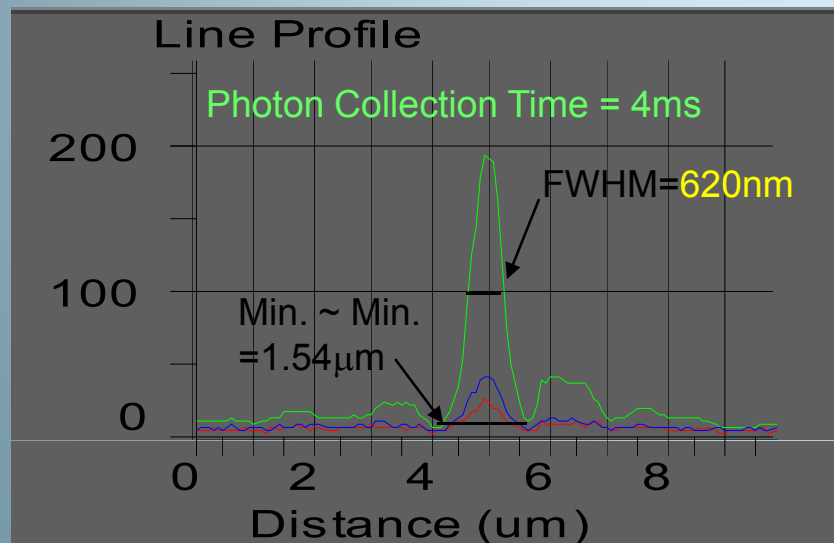


FOCAL POINT P1



FOCAL POINT PX

($2\mu\text{m}$ before destructive
interference height)



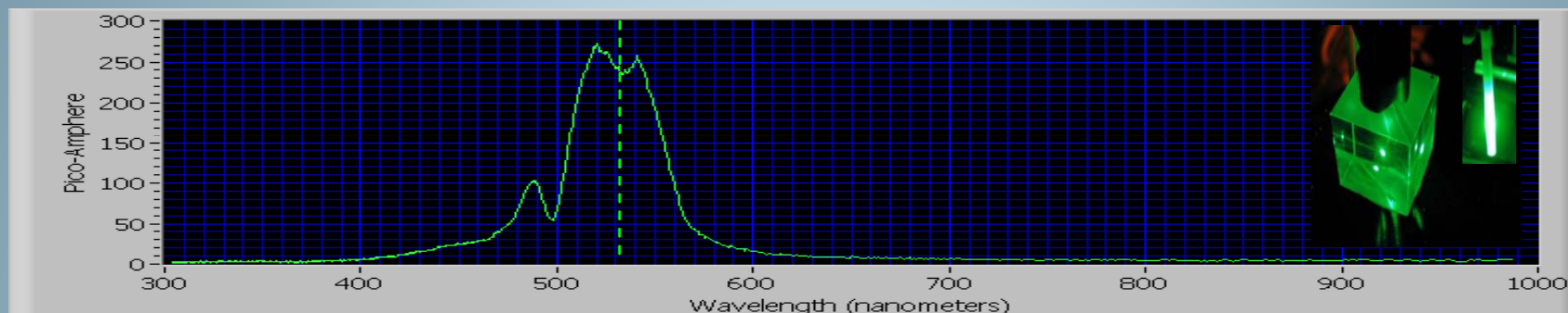
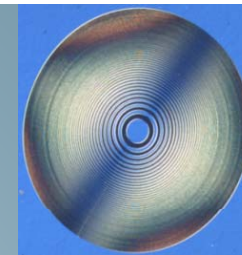
Photonic DART Technology
(Densely Accumulated Ray-point by micro-zone-plaTe)



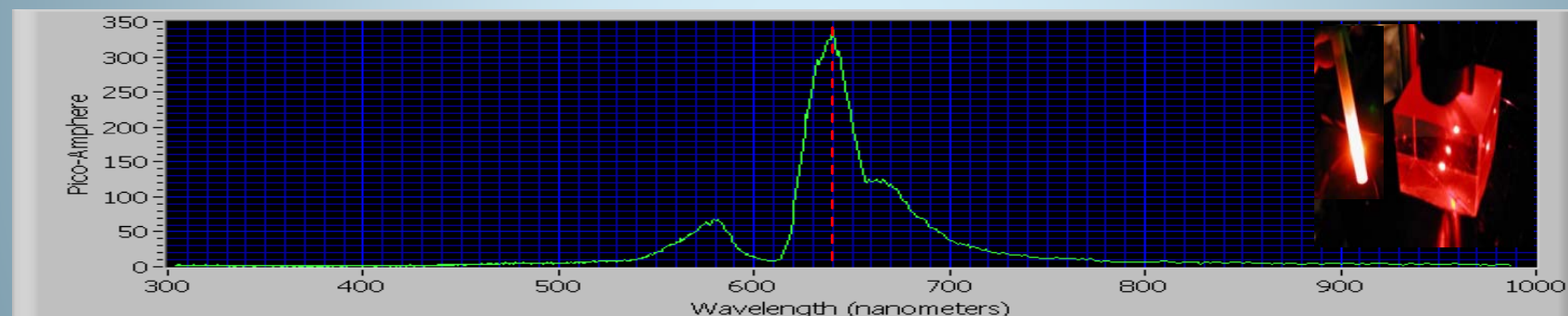
Spectral scans:

Circular Grating: 100 rings, 750 μ m diameter
Aperture: 10 μ m diameter

Green Laser: 532nm

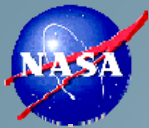


Red Laser: 633nm

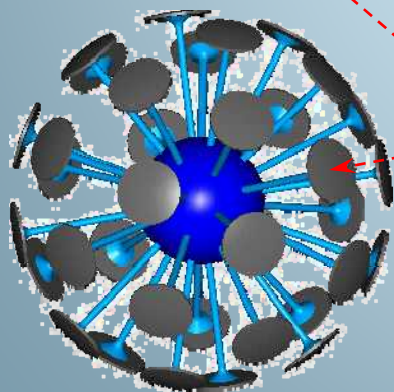
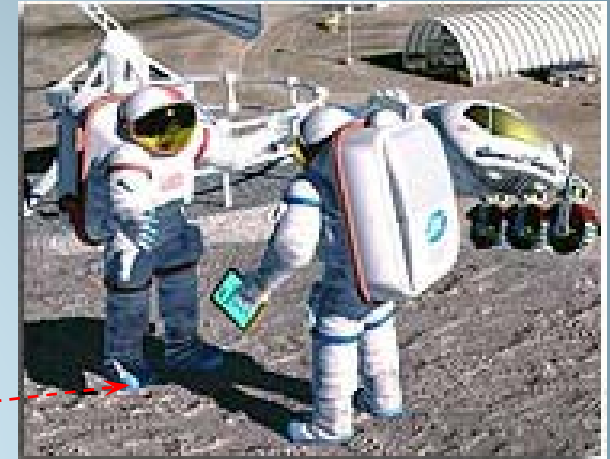
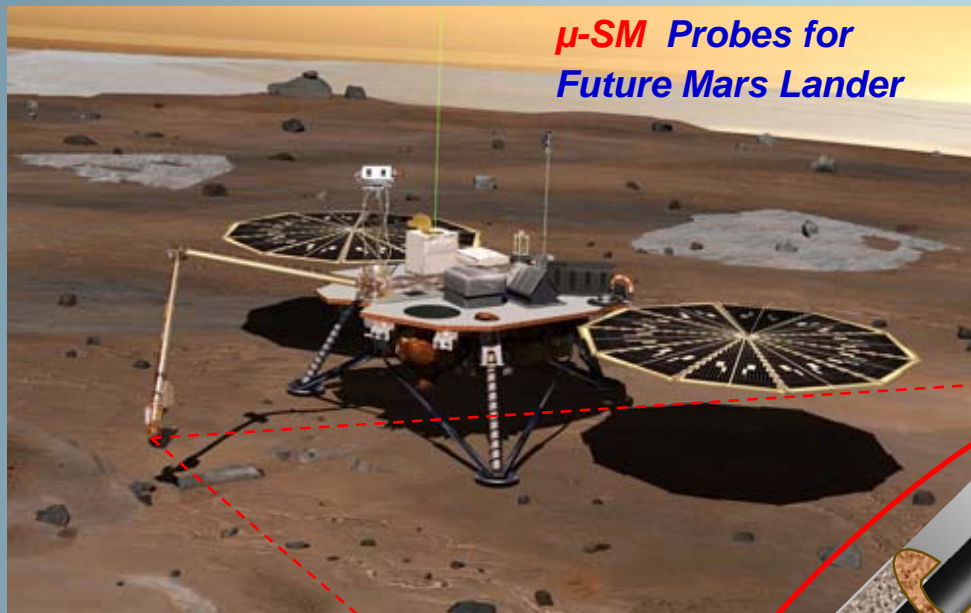


Green & Red Lasers: 532nm & 633nm

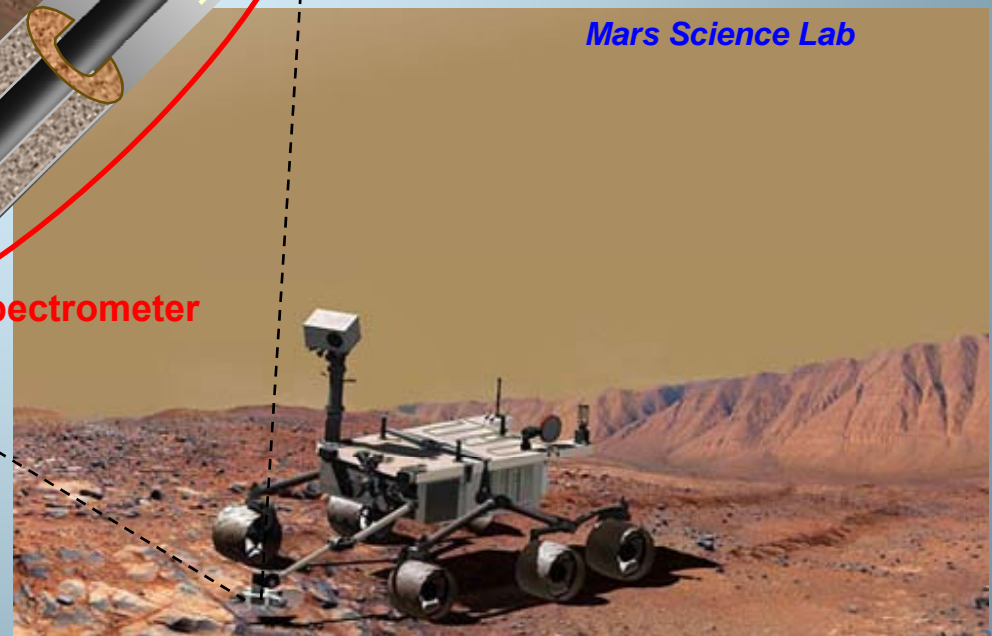
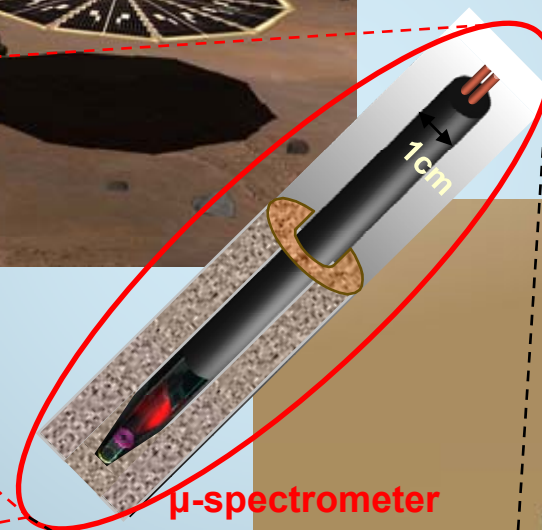




μ -Spectrometer (μ -SM) Applications Lunar & Mars Exploration

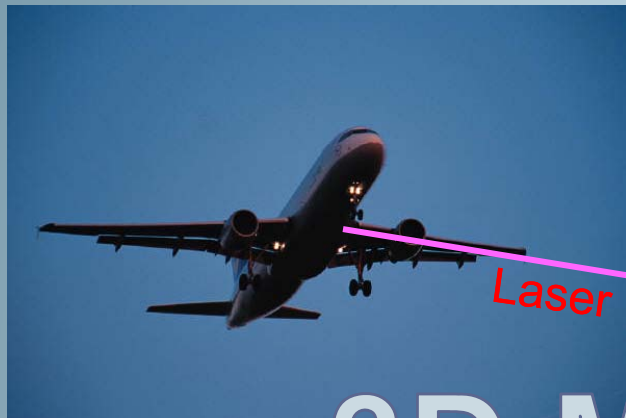


μ -SM imbedded Tumbleweed Rover

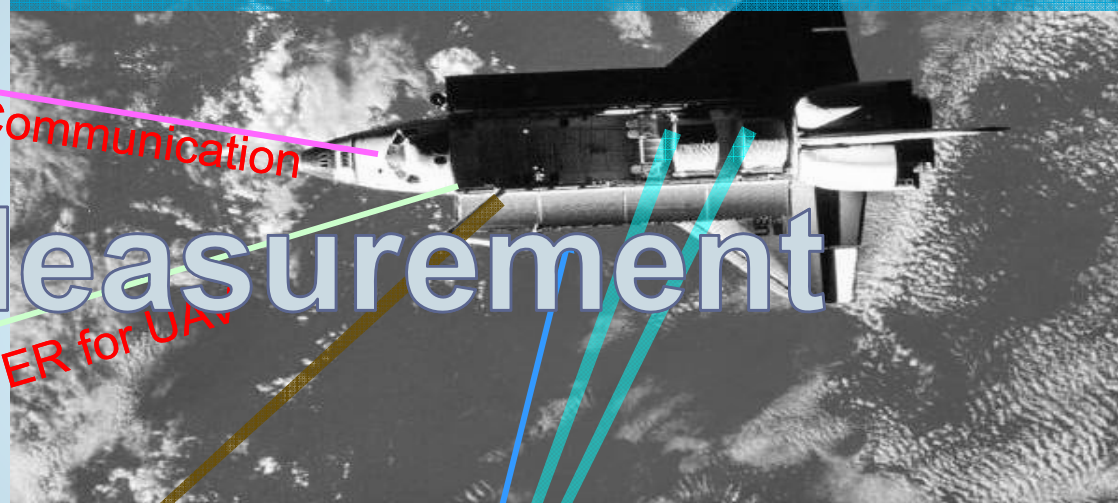




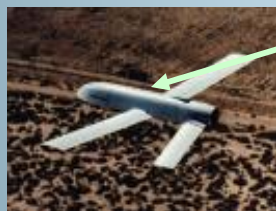
Aero-Space Application



Typical Mechanical Vibration: 0.1Hz ~ 100kHz
Beam scanner has to be faster than a few MHz!
We need Fast Solid State Optical Components!



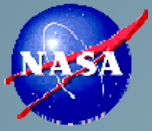
3D Measurement



2D Measurement

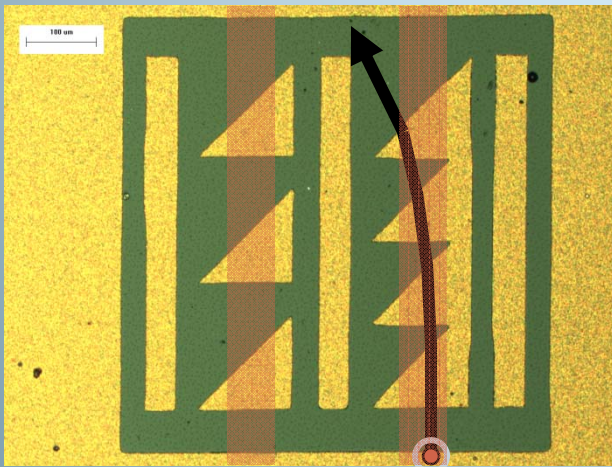


3D Measurement
Interference Fringe
Two Photon Excitation



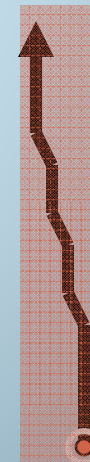
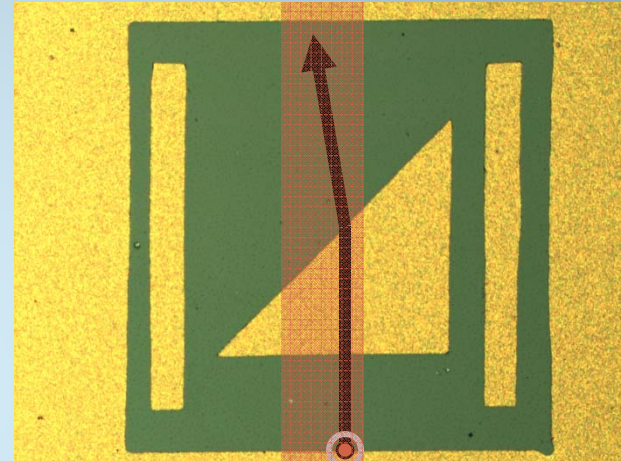
Lithography and Etched Patterns

E-Beam Lithography

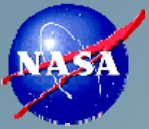


Beam Scanner Array

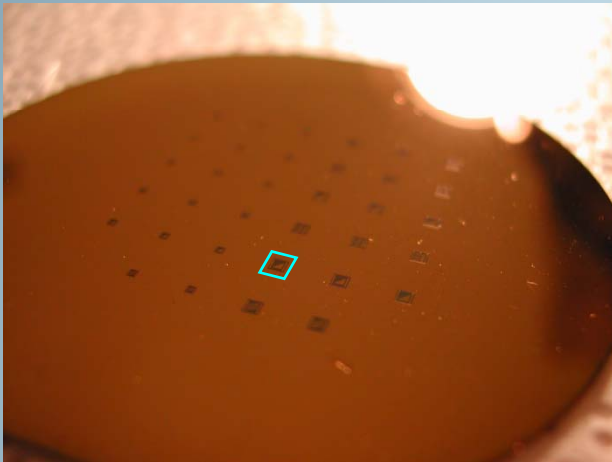
Single Beam Scanner



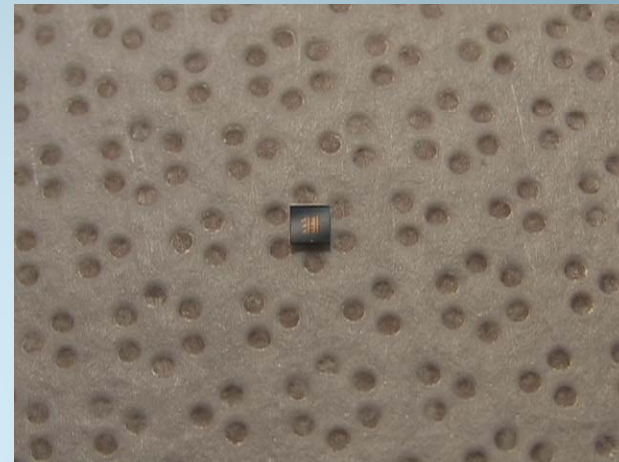
Beam Displacer



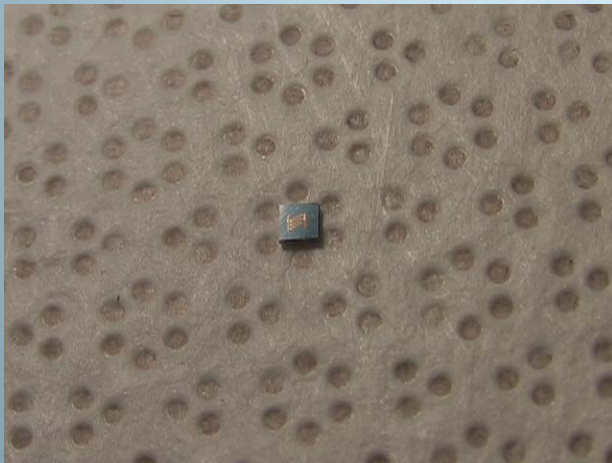
Light Control Device



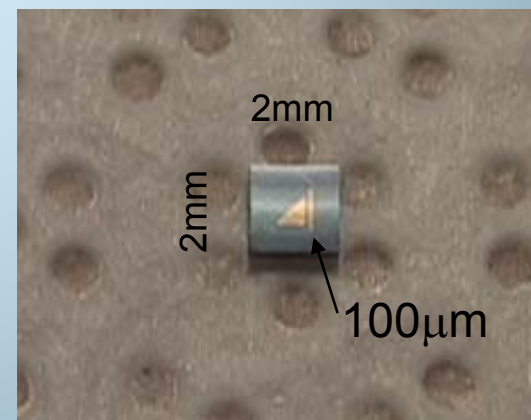
Patterns made with E-Beam Lithography



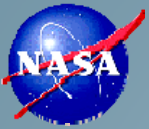
All-Solid-State Beam Scanner



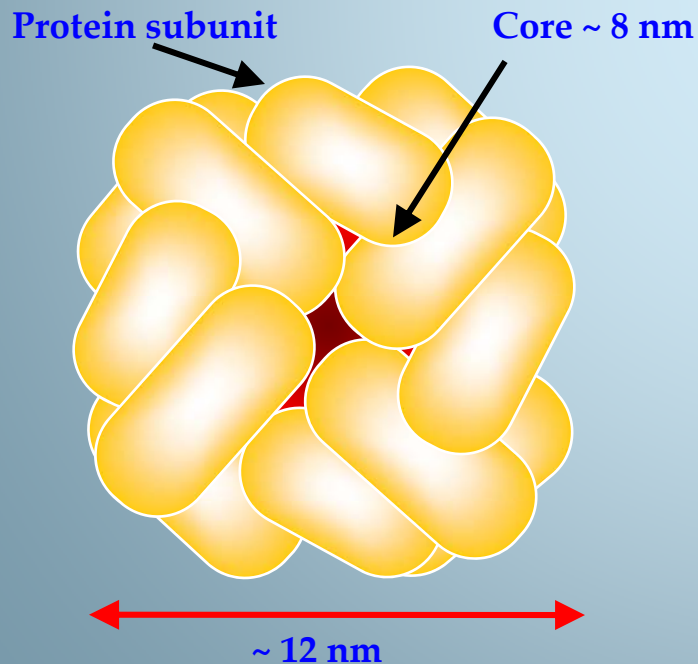
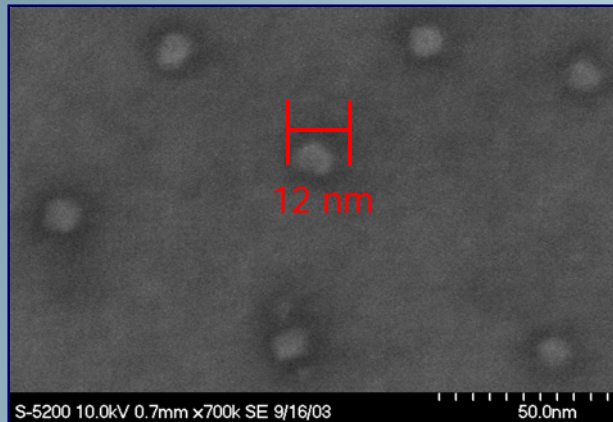
All S.S. Beam Scanner Array



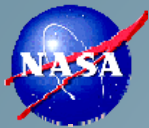
Solid State Beam Displacer



Ferritin Protein



- Iron storage protein in biological mechanisms in human, animal, and even bacteria
- 24 subunits
- Contains up to ~ 4500 Fe^{3+} atoms
- Stable and robust structure to withstand biologically extremes of high temperature (up to 80°C) and pH variations (2.0-10.0)
- 2, 3, 4-fold symmetry channels for the transport of ions and molecules.
- Hydrophilic 3 fold (Fe^{2+})/ Hydrophobic 4 fold
- Electron conduction through ferritin shell is possible.
- Core materials –
 - Iron (Fe), Cobalt (Co), Manganese (Mn), Nickel (Ni), Platinum (Pt), Semiconductors (CdS, CdSe)
 - Magnetite-maghemite
 - Trimethylamine-N-oxide, etc.

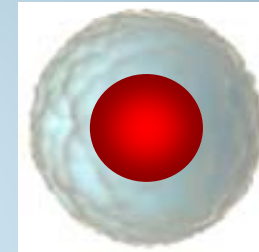


Biomining & Reconstitution of Ferritin Core

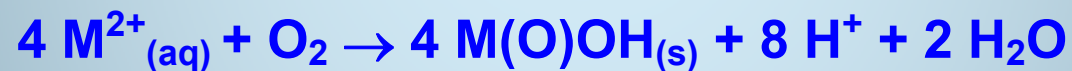


Apo-ferritin

M^{2+} , Oxidant



Ferritin reconstituted
with M^{3+}



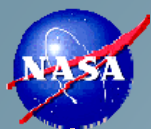
M : Core materials ---- Fe (natural)

Co, Mn, Ni, Pt, As, P, V (successful)

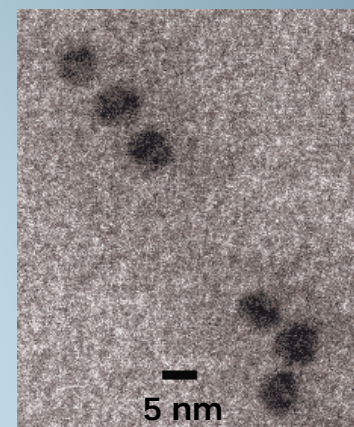
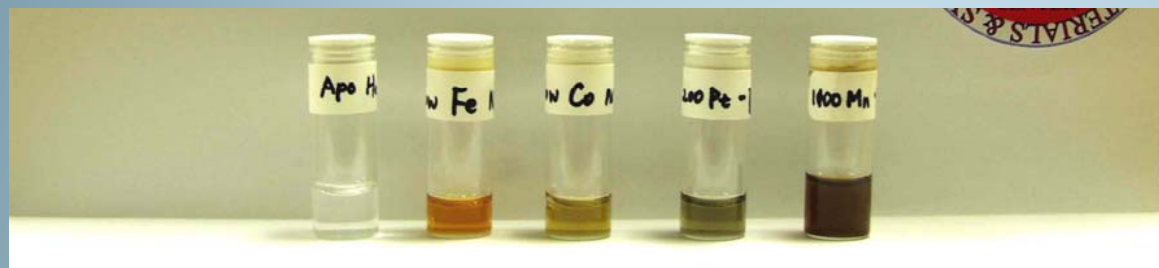
CdS, CdSe (successful)

Magnetite-maghemite (ferrimagnetic)

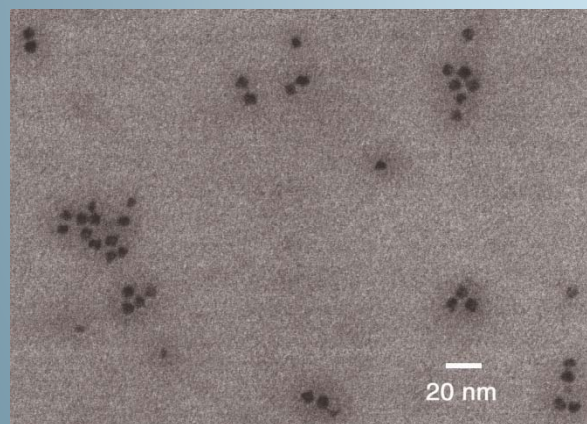
Trimethylamine-N-oxide (superparamagnetic)



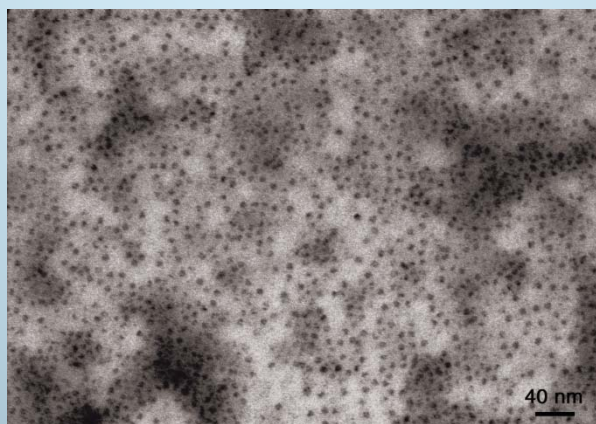
Chemically Reconstituted Ferritins



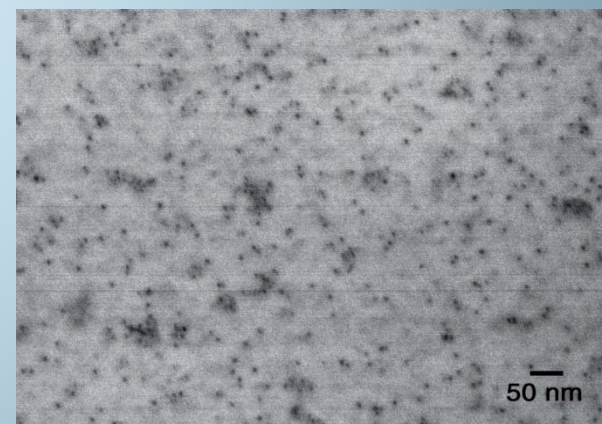
STEM image of Fe-cored ferritins



Fe-cored ferritins

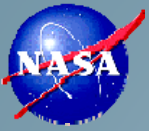


Co-cored ferritins



Mn-cored ferritins

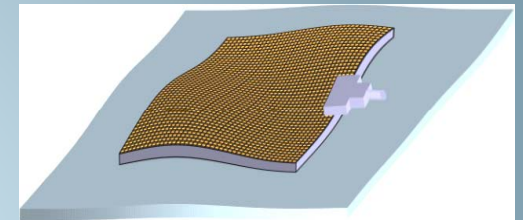
Inorg. Chem., **44**, 3738-3745 (2005).
Chem. Commun., (32), 4101 -4103 (2005).



Why Bio-Nanobattery ?

What about

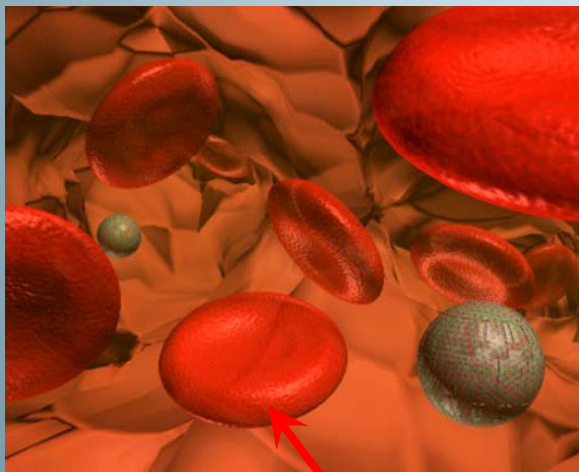
- **Distributed** power storage ?
- **Flexible thin-film** battery ? - Designer's dream !!
- **Easy embodiment** with power harvesting devices ?
- **Biocompatibility** with in-vivo nanodevices ?
- **Light weight** and high energy density ?
- **Chip scale power source** ?
 - Intelligent and autonomous operation



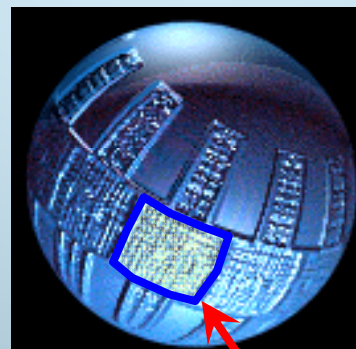
Flexible Nanobattery Film



Wearable Electronics (Philips)



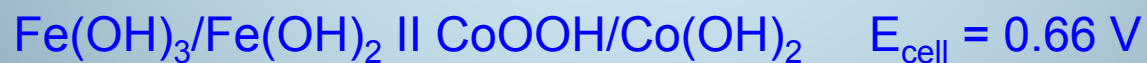
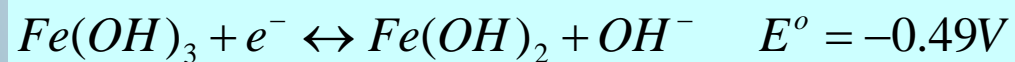
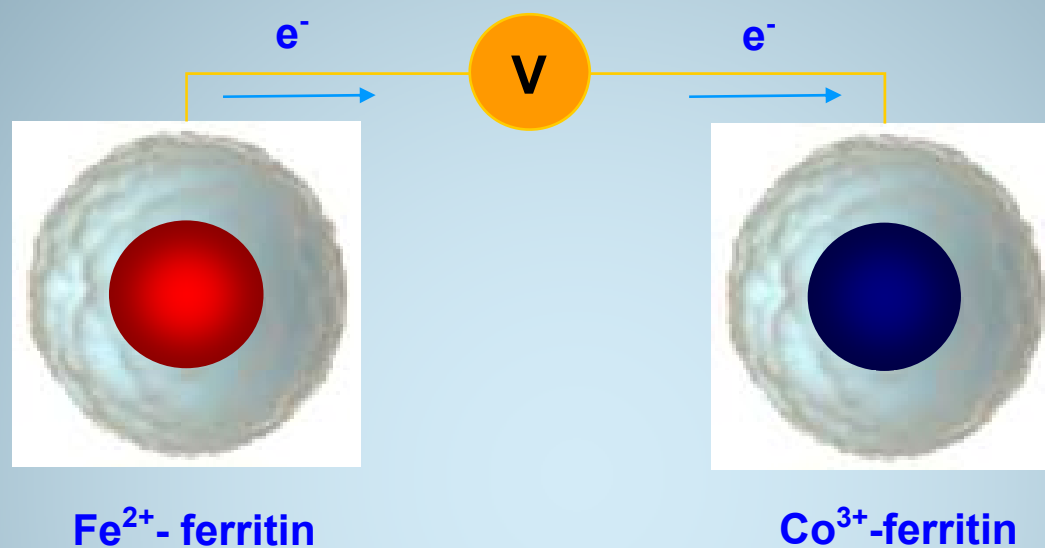
Red Blood Cell

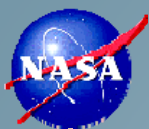


Bio-nanobattery patch installed
in autonomous bio-nanorobot



Bionanobattery Concept





Theoretical Values of Bionanobattery

→ Anode

↓ Cathode

	Zn	Cd	Fe	V	Hg	Mn	Co	Ni
Zn								
Cd	0.422							
Fe	0.756	0.334						
V	0.760	0.338	0.004					
Hg	1.344	0.922	0.588	0.584		0.388		
Mn	0.956 (1.606)*	0.534 (1.184)	0.200 (0.850)	0.196 (0.846)	(0.262)		(0.190)	
Co	1.416V	0.994	0.660	0.656	0.072	0.120		
Ni	1.726	1.304	0.970	0.966	0.382	0.770	0.310	

$\text{Zn}^0/\text{Zn}^{2+}$: -1.246 V

$\text{Cd}^0/\text{Cd}^{2+}$: -0.824 V

$\text{Fe}^{2+}/\text{Fe}^{3+}$: -0.49 V

$\text{V}^{2+}/\text{V}^{3+}$: -0.486 V

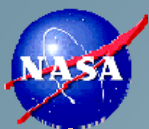
$\text{Hg}^0/\text{Hg}^{2+}$: 0.098 V

$\text{Mn}^{2+}/\text{Mn}^{3+}$: -0.29 V

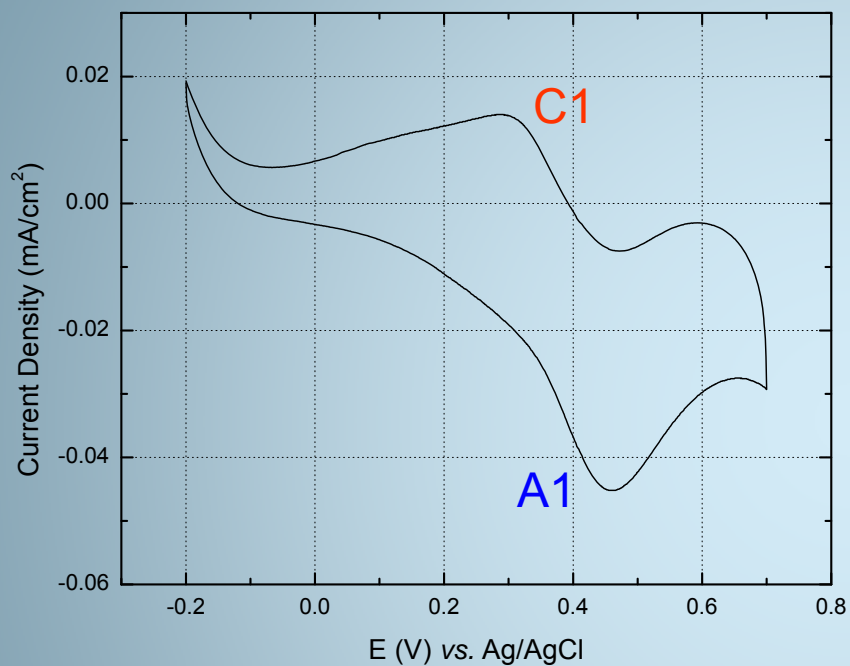
$\text{Co}^{2+}/\text{Co}^{3+}$: 0.17 V

$\text{Ni}^{2+}/\text{Ni}^{3+}$: 0.48 V

(*) Mn represents as $\gamma\text{-MnO}_2$ inside Ferritin.

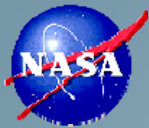


Ni-Cored Ferritin



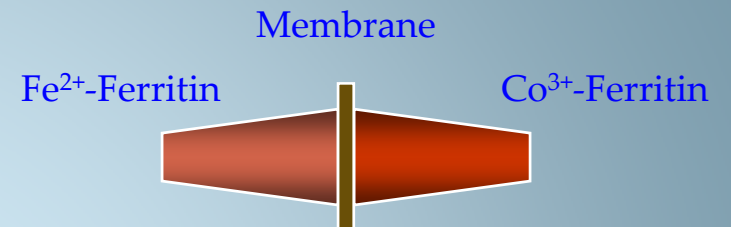
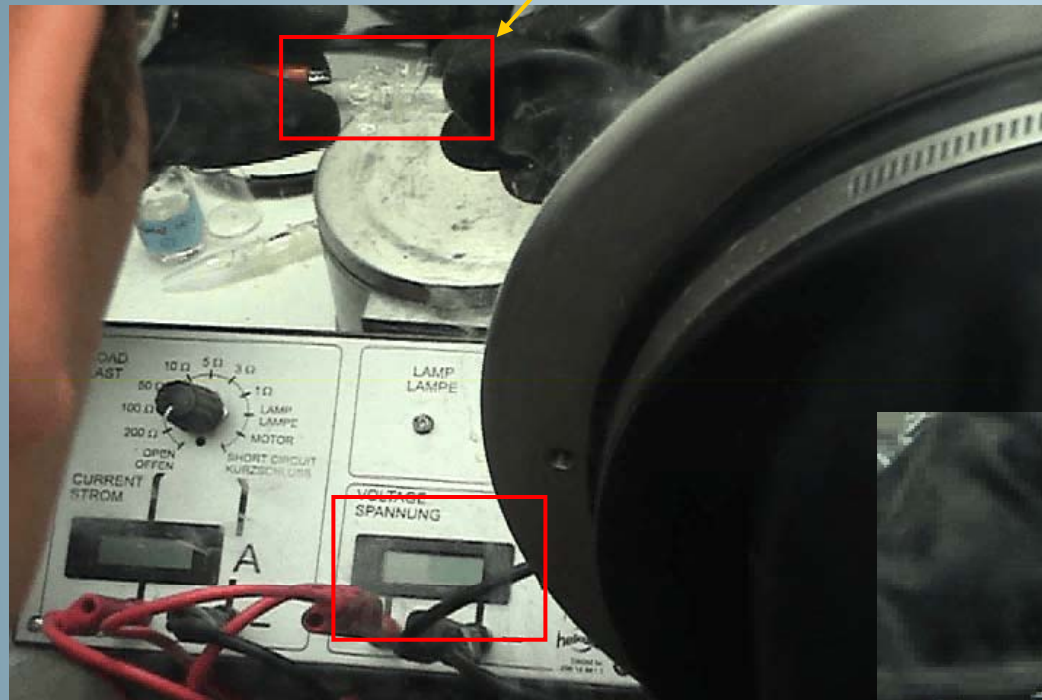
CV of physically adsorbed Ni-cored ferritin on Au electrode in 0.05 M phosphate buffer (pH 7.5 and pH 9.0) at the scan rate of 100 mV/s.

	Co	Mn	Ni
Fe	500 mV	480 mV	790 mV

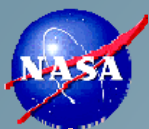


Fe-Co Bionanobattery Cell – Wet Cell

Bionanobattery Demo Cell



0.46 V / Unit Cell



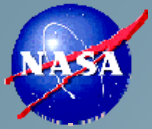
Fe-Co Bionanobattery Cell – Solid Electrodes



Thiolated $\text{Fe}^{2+} \Rightarrow$ thiolated Co^{3+}

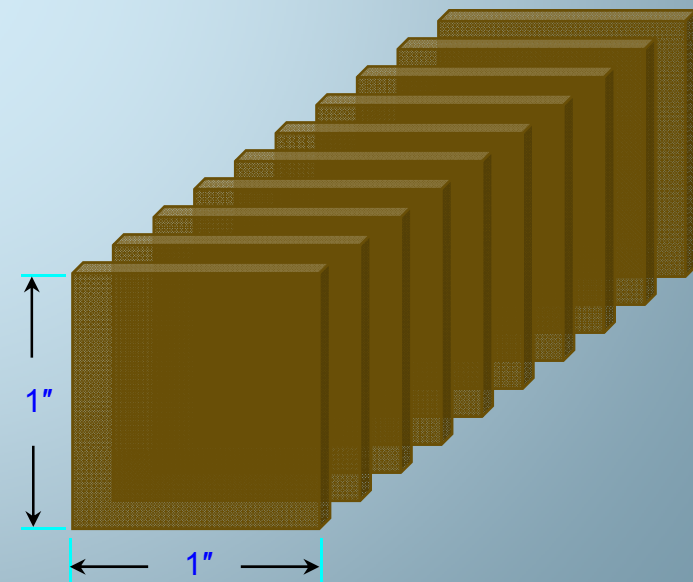
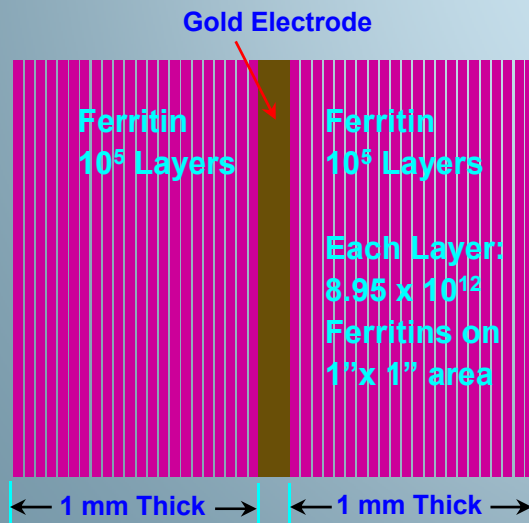
0.25 V / Unit Cell

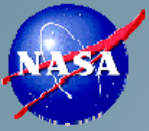




Estimation of Electrical Output

- Electrode: 1"x1" gold films coated on both sides of a quartz slide
- Total number of ferritin on each layer of 1" x 1" area: 4.48×10^{12}
- Total available electrons: 2×10^{16} per layer = 3.2×10^{-3} Coulomb
- Charge Density per Electrode (2×10^5 layers): 640 Coulomb
- Cell Charge Density (array of 10 electrodes): 6400 Coulomb
- Operational Run-time: 6400 seconds when Fe^{2+} - Co^{3+} electrodes discharge 1 C/sec
- If we connect 10 gold electrodes together, then
 - Parallel connection: 0.79 V, 1 A (2844 mWh)
 - Serial connection: 7.9 V, 100 mA





Conclusion

The areas discussed are still under development.

- Nano structured materials for TE applications
 - SiGe and Be-Te
 - Nano particles and nanoshells
- Quantum technology for optical devices
 - Quantum apertures
 - Smart optical materials
 - Micro spectrometer
- Bio-template oriented materials
 - Bionanobattery
 - Biofuel cells
 - Energetic materials